

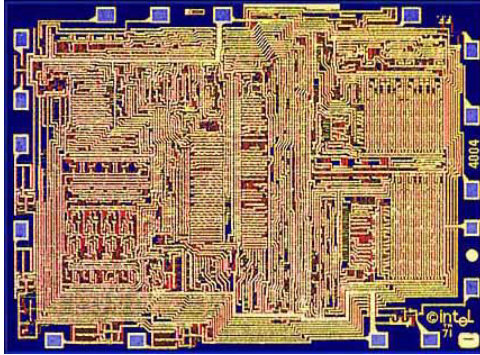
# Basics of VLSI Design and IP

Prof. Maurizio MARTINA

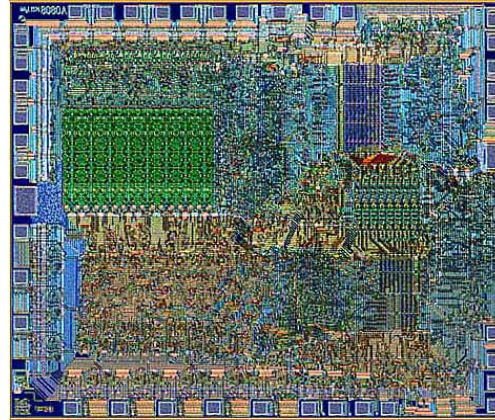
# Introduction to VLSI Design

- VLSI Design: Very Large Scale Integration Design
  - Complex design
  - Large digital part
  - Massive production

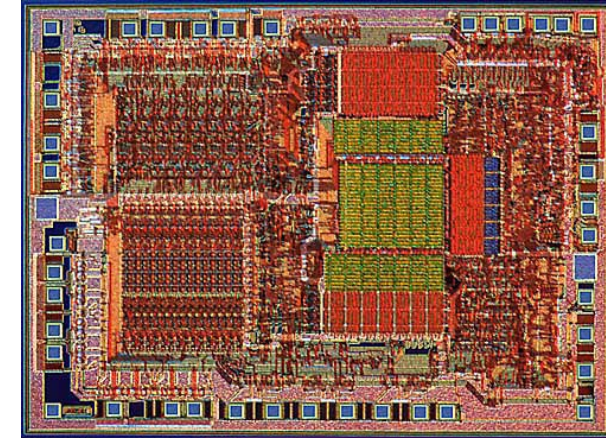
# Evolution of VLSI technology



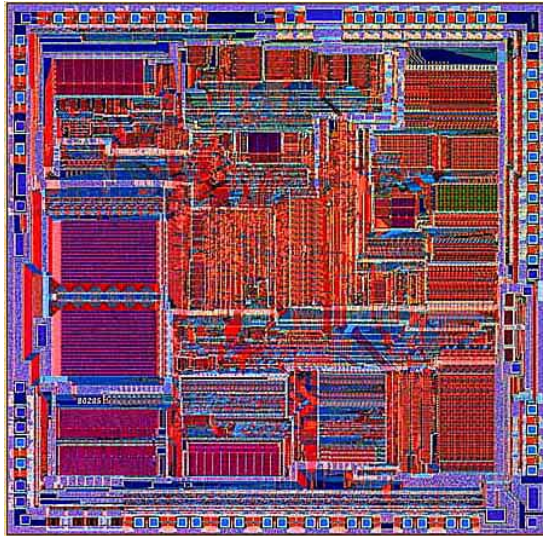
Intel 4004 ('71)



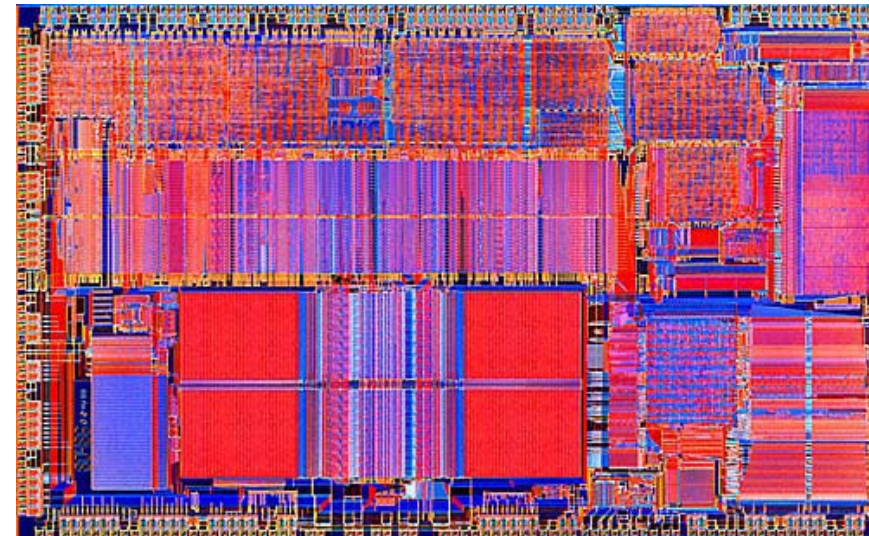
Intel 8080



Intel 8085

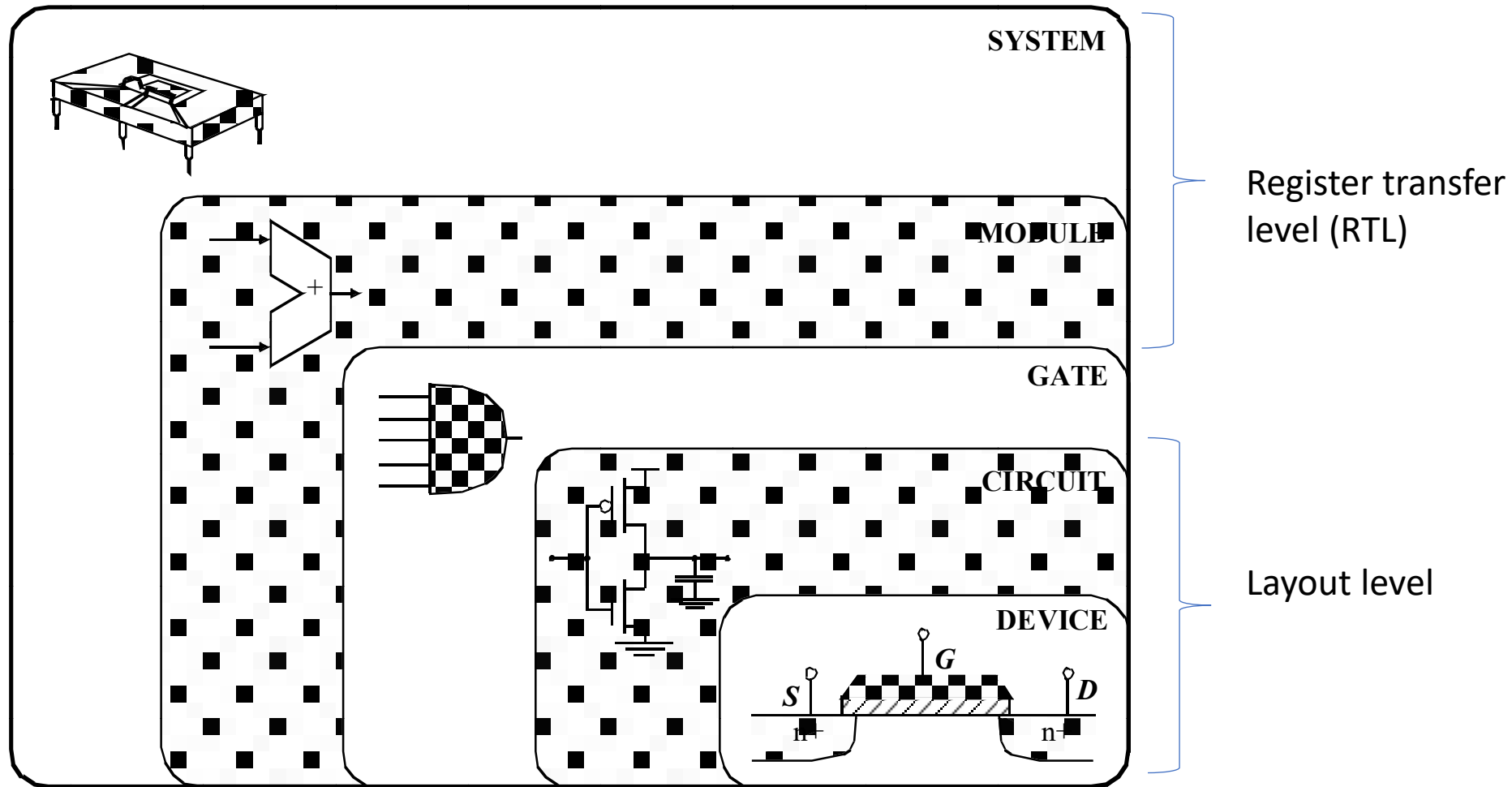


Intel 8286



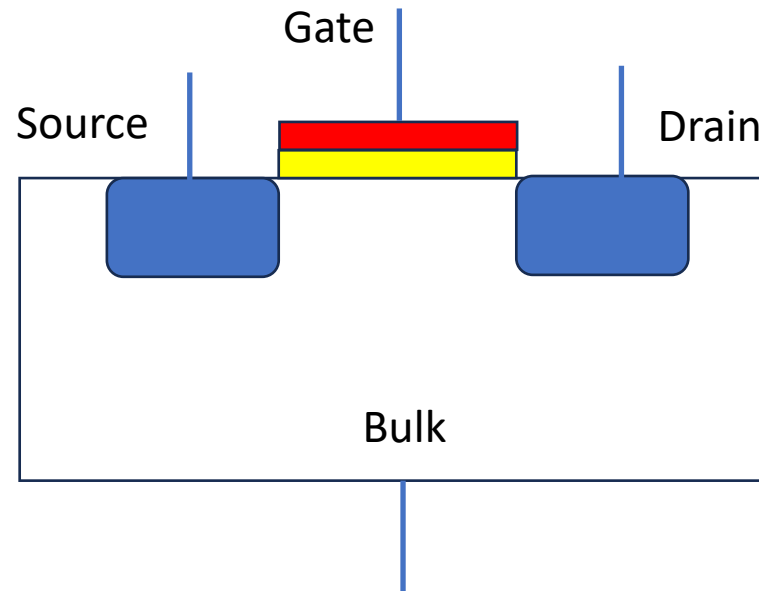
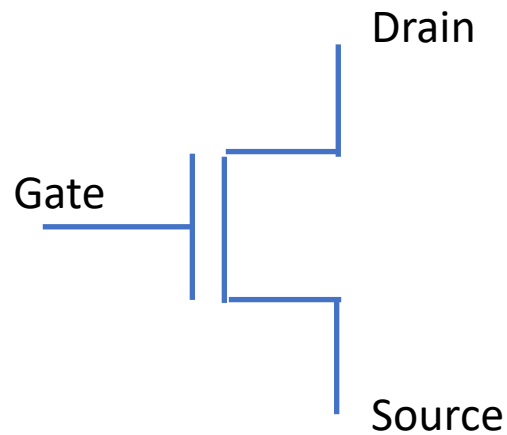
Intel 8486

# VLSI design process overview



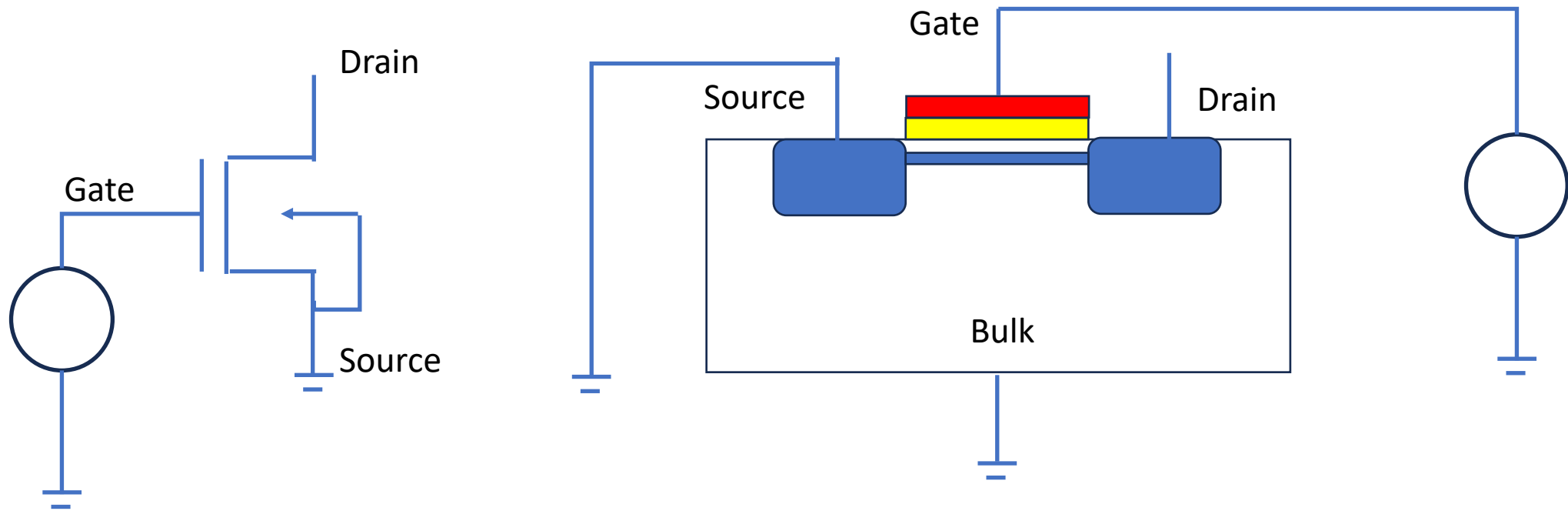
# Device - I

- MOS (Metal-Oxide-Semiconductor) Transistor model



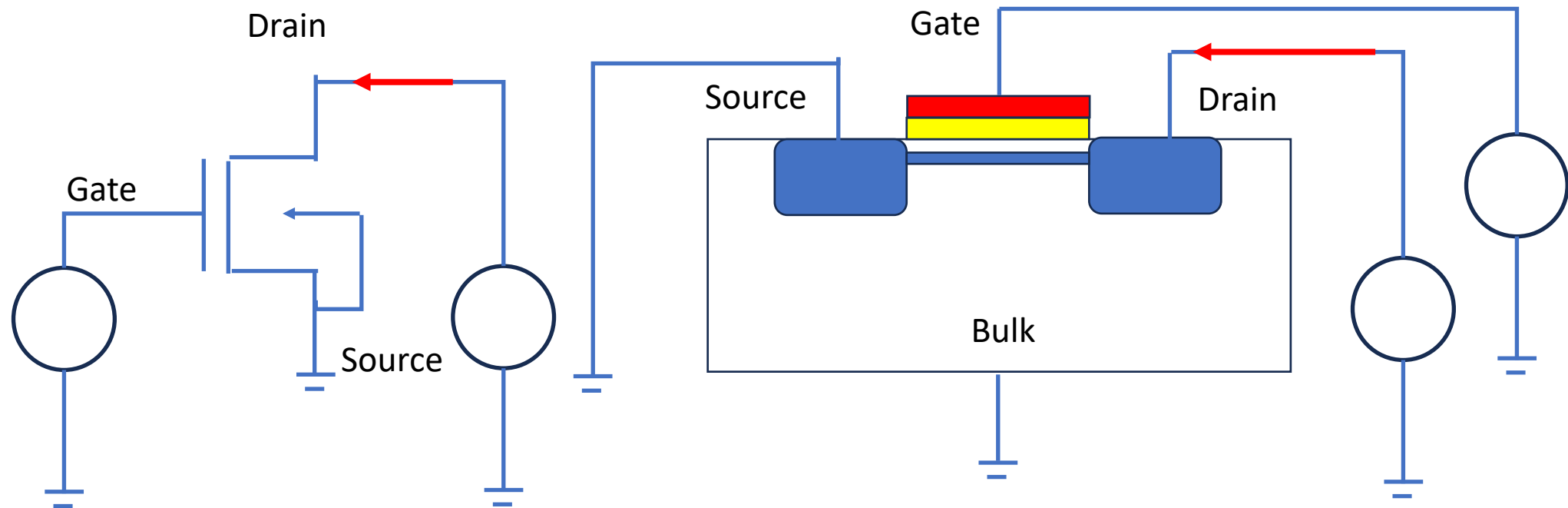
# Device - II

- MOS (Metal-Oxide-Semiconductor) Transistor model



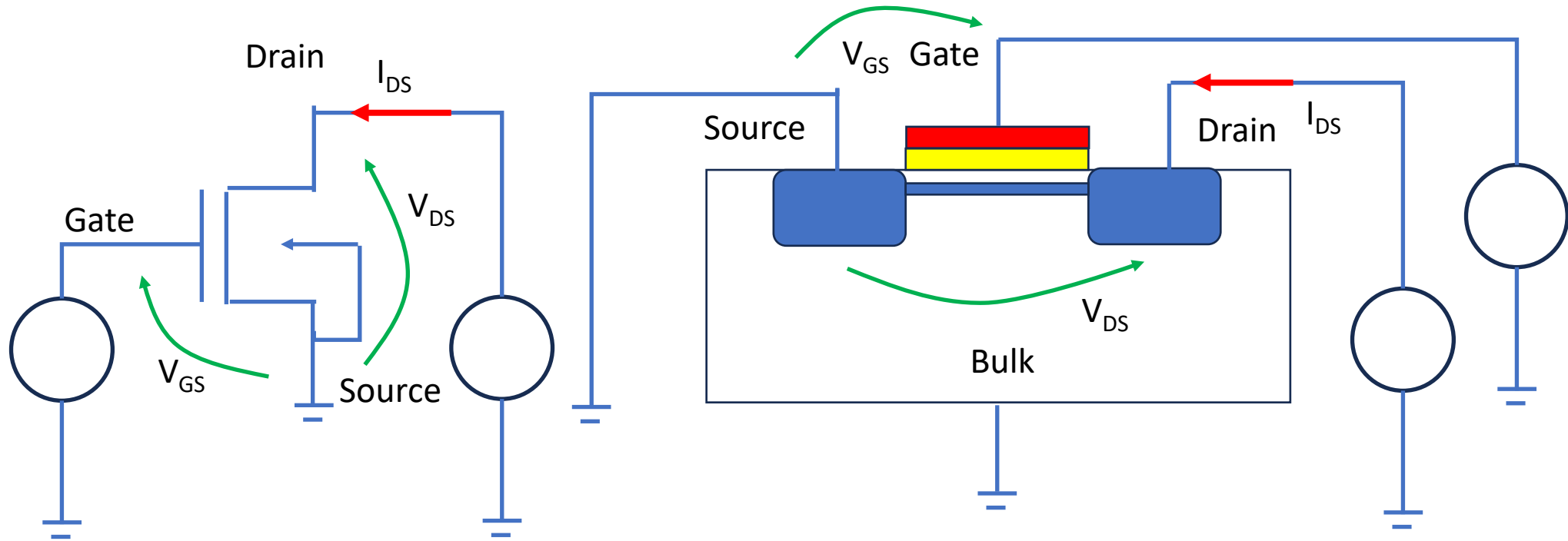
# Device - III

- MOS (Metal-Oxide-Semiconductor) Transistor model



# Device - IV

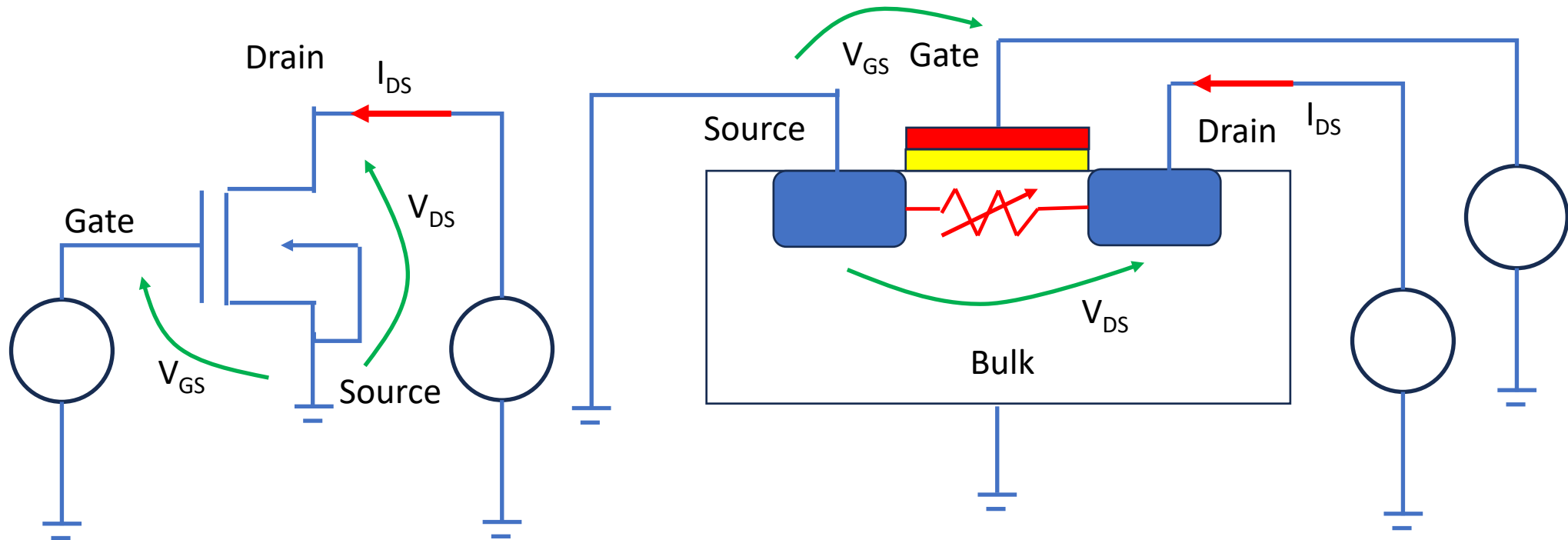
- MOS (Metal-Oxide-Semiconductor) Transistor model





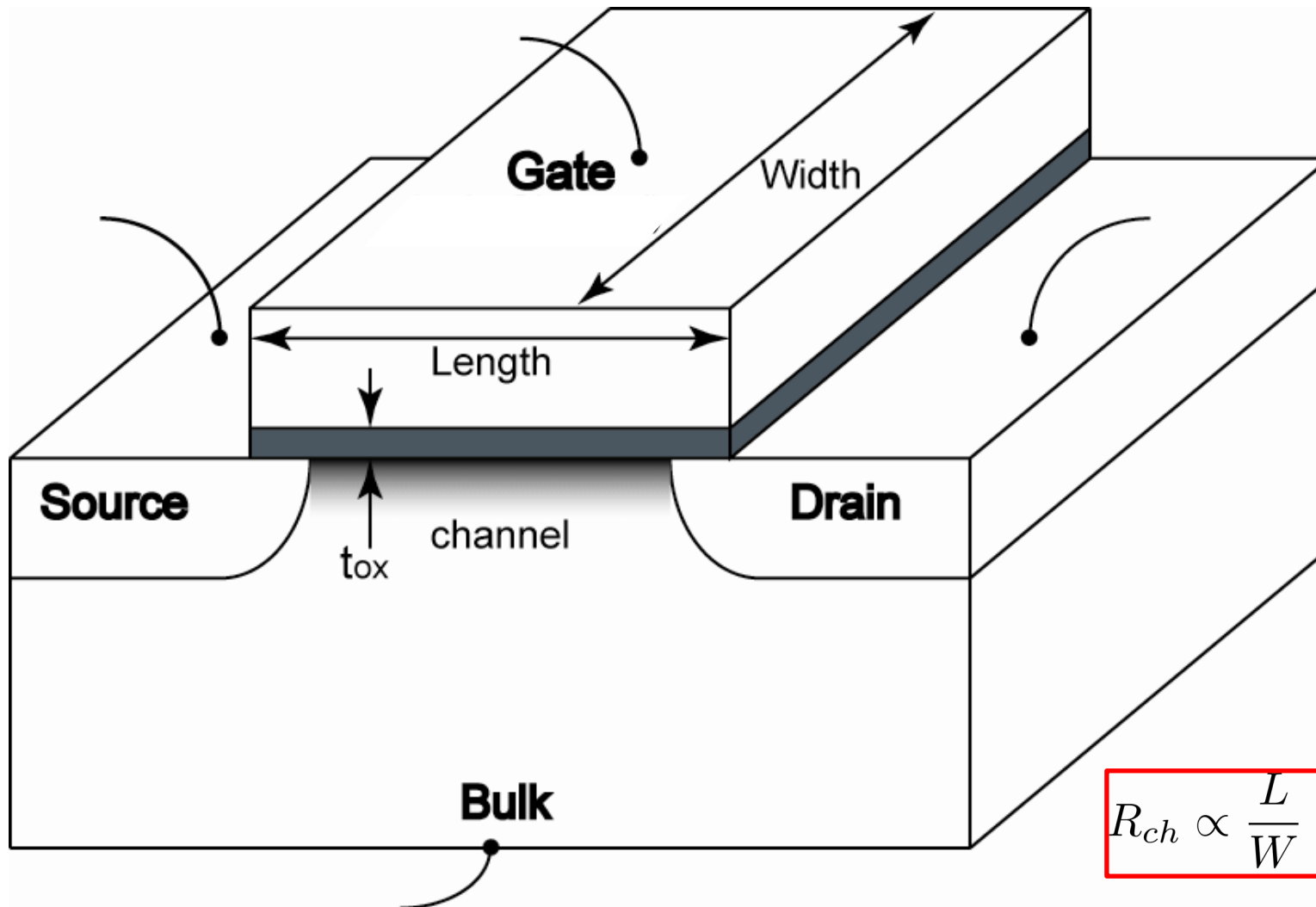
# Device - V

- MOS (Metal-Oxide-Semiconductor) Transistor model



$$I_{DS} = f(V_{GS}, V_{DS})$$

# 3D view



- The channel resistance depends also on geometrical parameters: Length (L) and Width (W)

$$R_{ch} \propto \frac{L}{W} \rightarrow I_{DS} \propto \frac{V_{DS}}{R_{ch}} \rightarrow I_{DS} \propto \frac{W}{L} V_{DS}$$

# MOS transistor triode current

- It can be shown<sup>(\*)</sup> that:

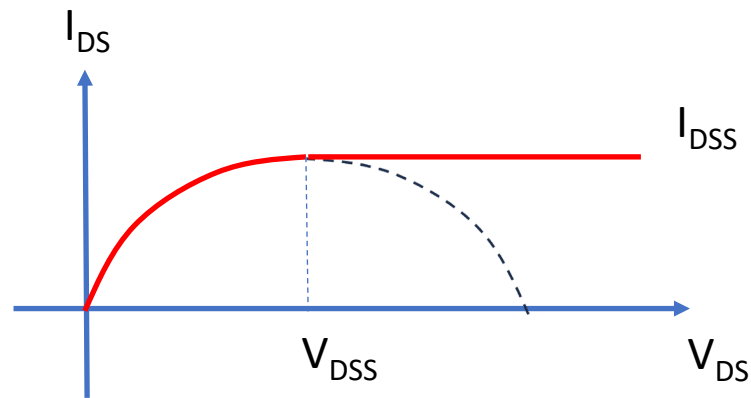
$$I_{DS} = \mu C_{ox} \frac{W}{L} \left[ (V_{GS} - V_T) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

- where we have parameters that depend on:
  - Technology
    - $\mu, C_{ox}, V_T \rightarrow$  carriers mobility, oxide capacitance, threshold voltage
  - Circuit
    - $V_{GS}, V_{DS}$
  - Geometry
    - $W, L$

(\*) R. Muller, T. Kamins "Device Electronics for Integrated Circuits"

# Saturation

- The triode equation shows parabolic behaviour of  $I_{DS}$  as a function of  $V_{DS}$
- Experimental results show that when the current reaches the maximum, it remains constant  $\rightarrow$  saturation !



$$\frac{\partial I_{DS}}{\partial V_{DS}} = 0 \rightarrow k [(V_{GS} - V_T) - V_{DS}] = 0$$

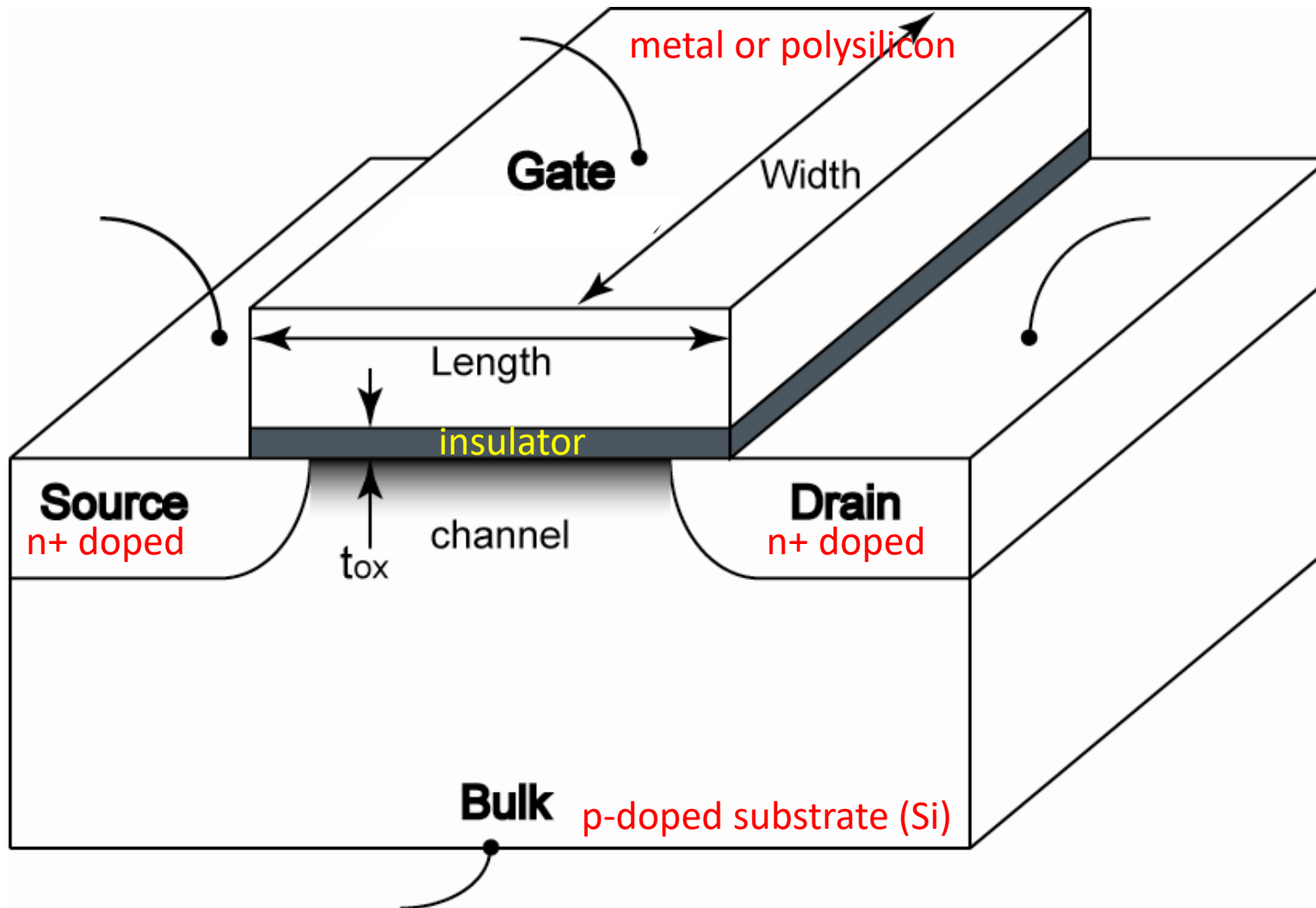


$$V_{DSS} = V_{GS} - V_T \rightarrow I_{DSS} = \frac{\mu C_{ox}}{2} \frac{W}{L} (V_{GS} - V_T)^2$$

# Digital circuits

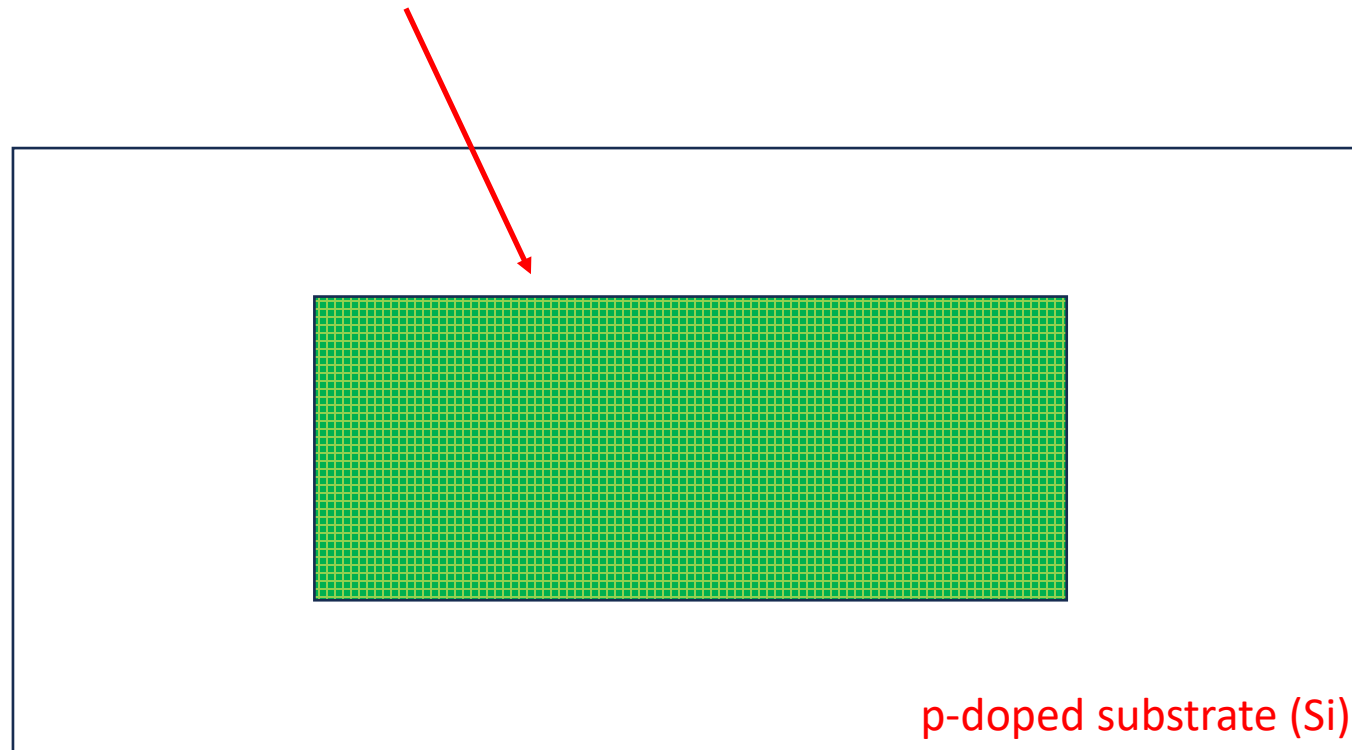
- $V_{GS}, V_{DS} \rightarrow$  low (gnd) or high ( $V_{dd}$ )
  1.  $V_{GS} = \text{low}, V_{DS} = \text{low} \rightarrow$  Transistor off  $\rightarrow I_{DS}=0$
  2.  $V_{GS} = \text{low}, V_{DS} = \text{high} \rightarrow$  Transistor off  $\rightarrow I_{DS}=0$
  3.  $V_{GS} = \text{high}, V_{DS} = \text{low} \rightarrow$  Transistor on, but  $I_{DS} \approx 0$
  4.  $V_{GS} = \text{high}, V_{DS} = \text{high} \rightarrow$  Saturation  $\rightarrow I_{DS}=I_{DSS}$
- Thus, given technology parameters, the designer can work on width (W) and length (L) of the MOS transistor.

# Technology details: nMOS transistor



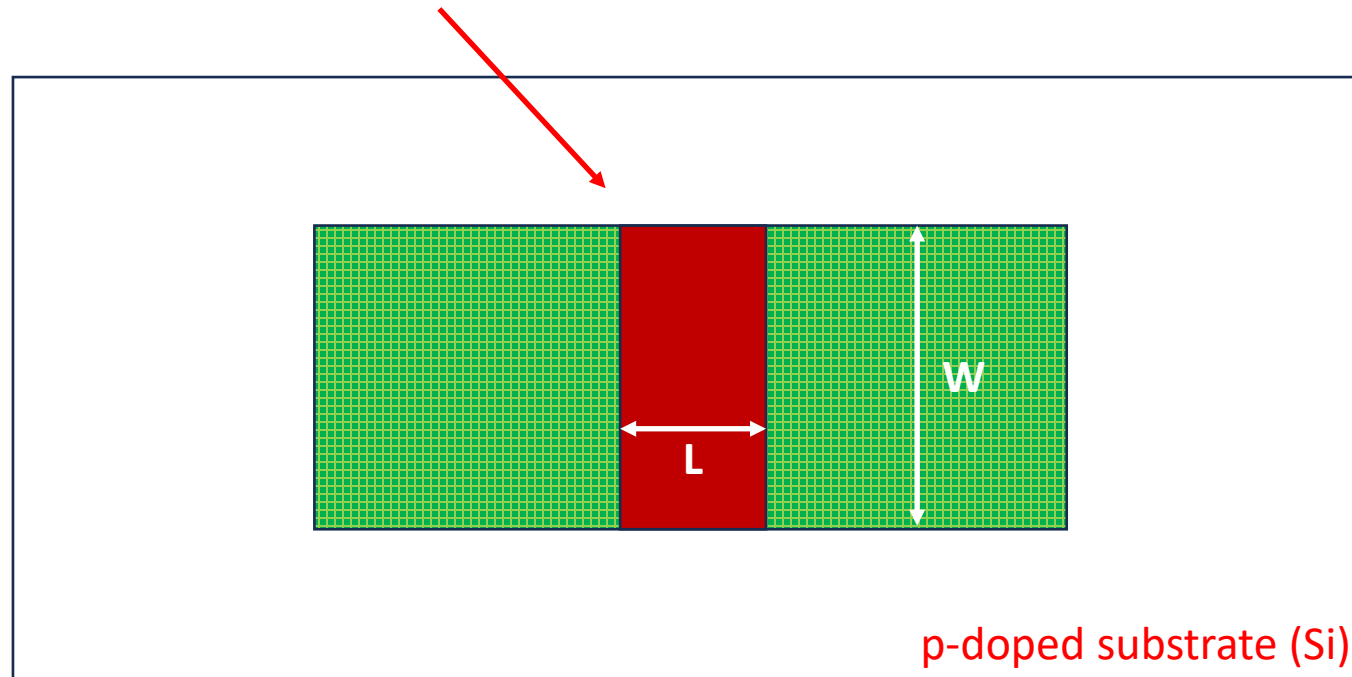
# Technology steps - I

- Top view:
  - Define the n-region, where the nMOS is built.



# Technology steps - II

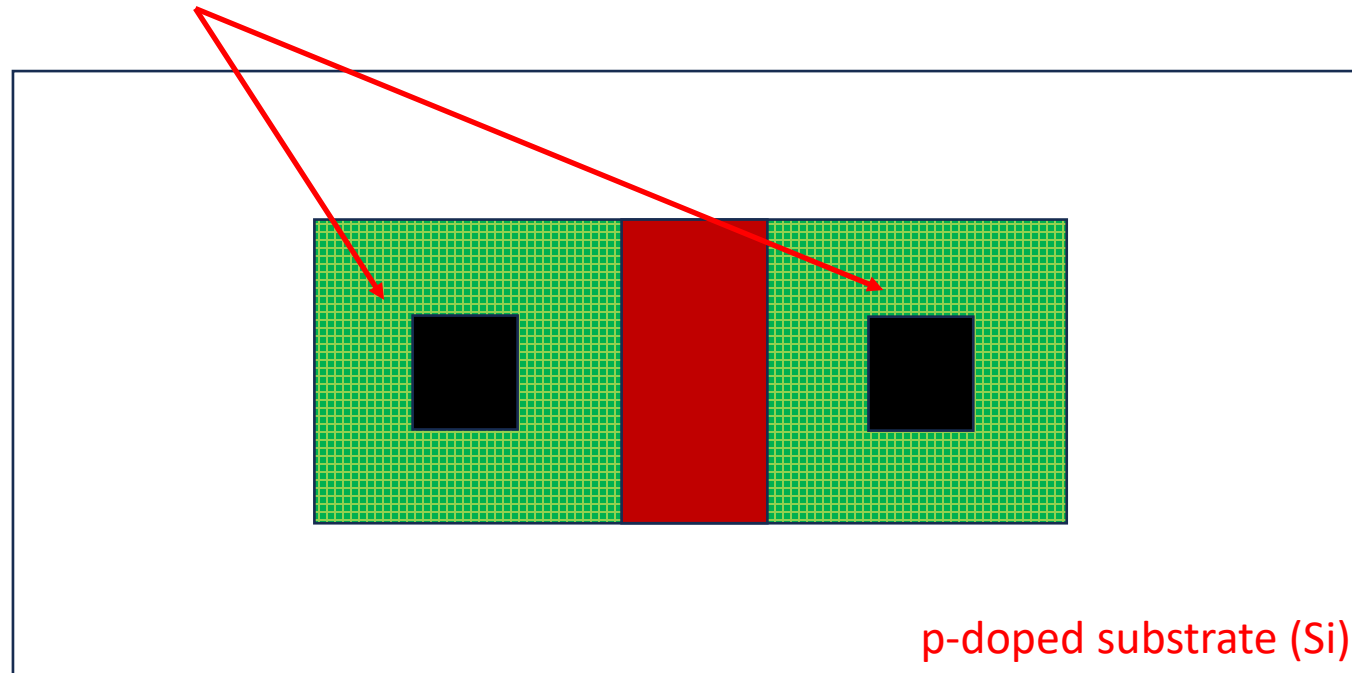
- Top view:
  - Define the n-region, where the nMOS is built.
  - Define the gate region of the nMOS





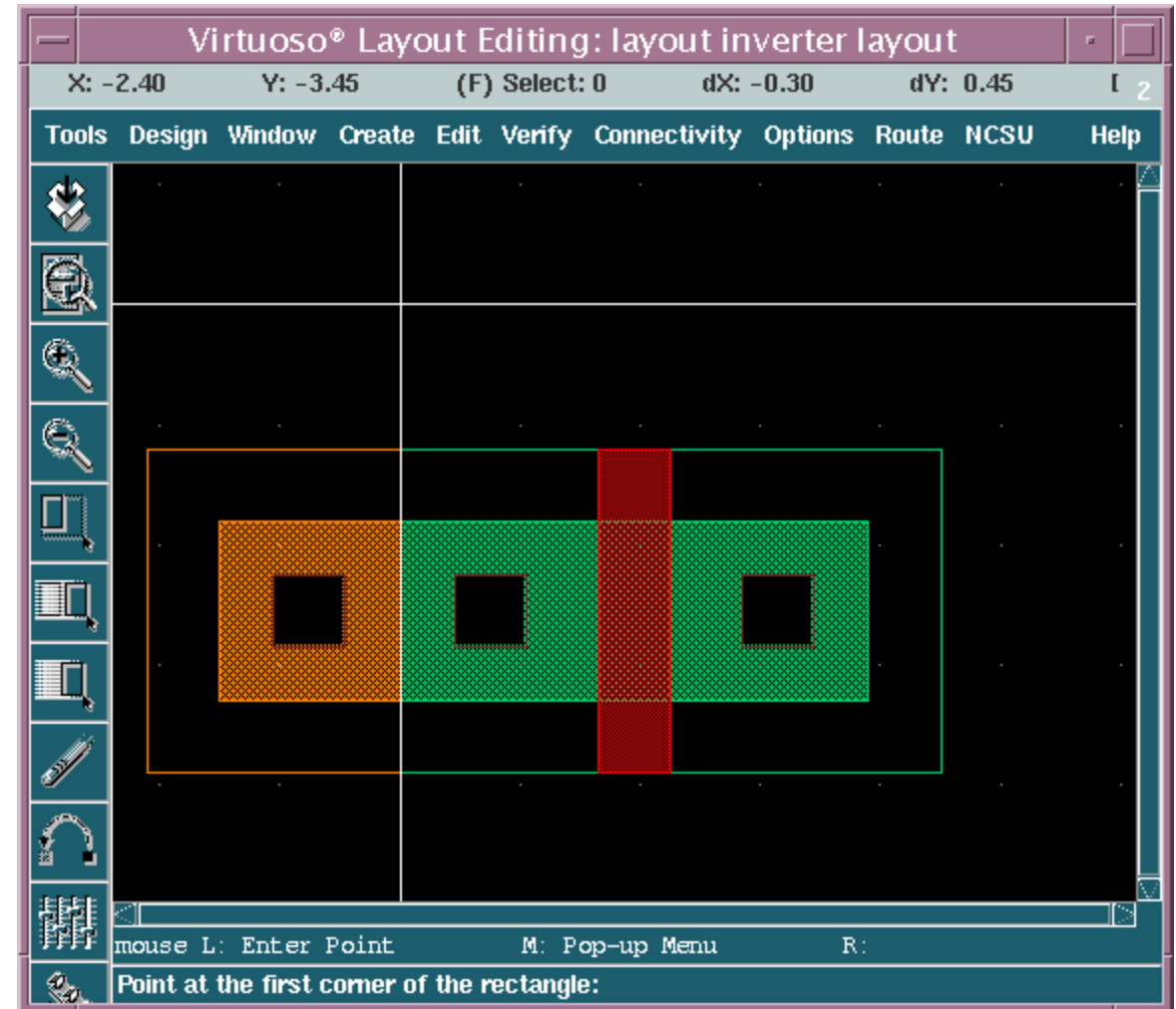
# Technology steps - III

- Top view:
  - ...
  - Add source and drain metal contacts



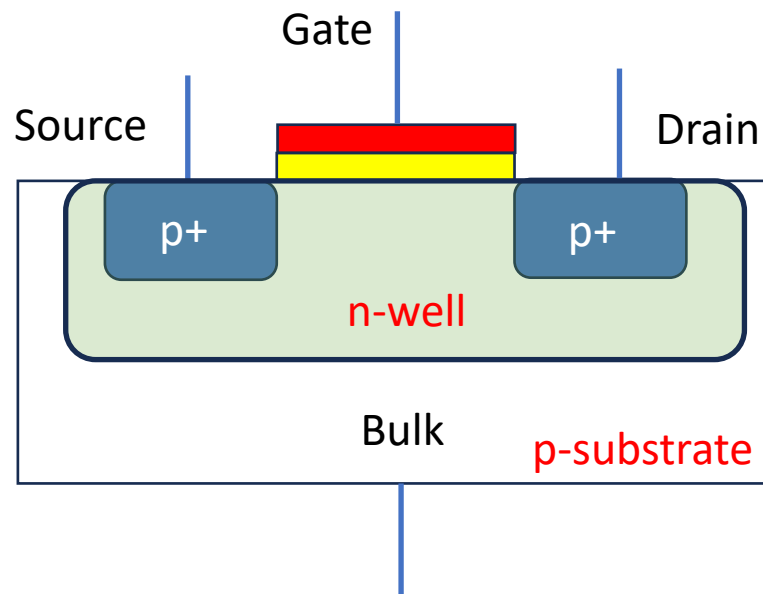
# Note: design rules

- Technology imposes some **design rules**:
  - Minimum feature size;
  - Minimum distance between different layers;
  - ...
- Example: real nMOS layout with substrate contact (orange square)



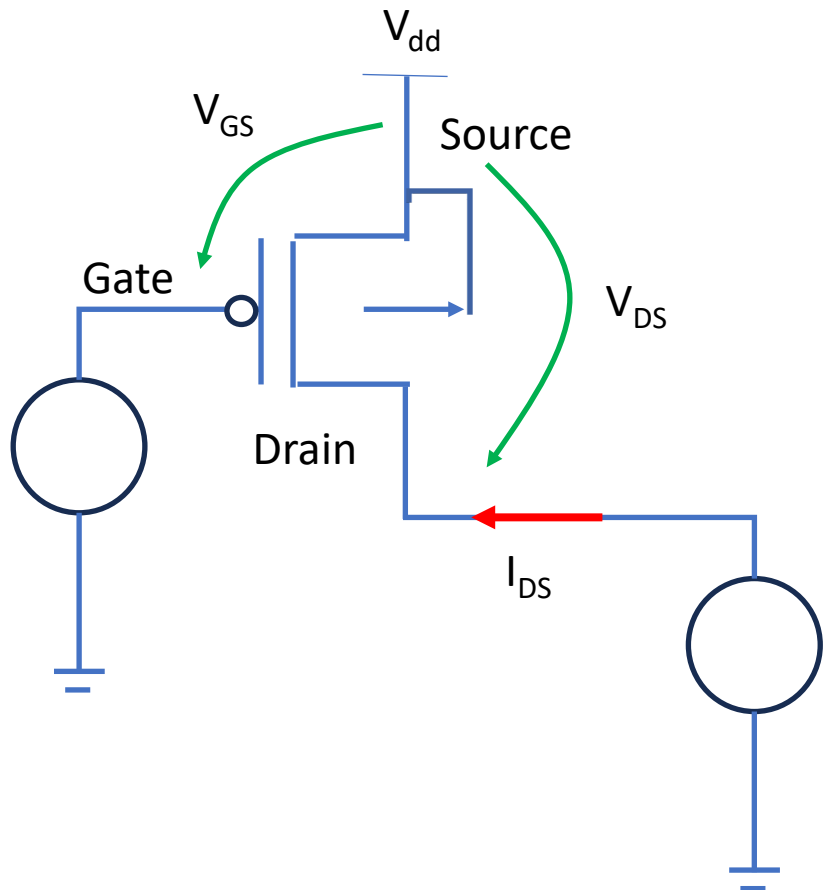
# pMOS transistor - I

- Building a pMOS transistor on a p-doped substrate seems not possible.
- We need to build an n-doped well and then we can build a pMOS.



# pMOS transistor - II

- It has a complementary behaviour with respect to nMOS transistors.



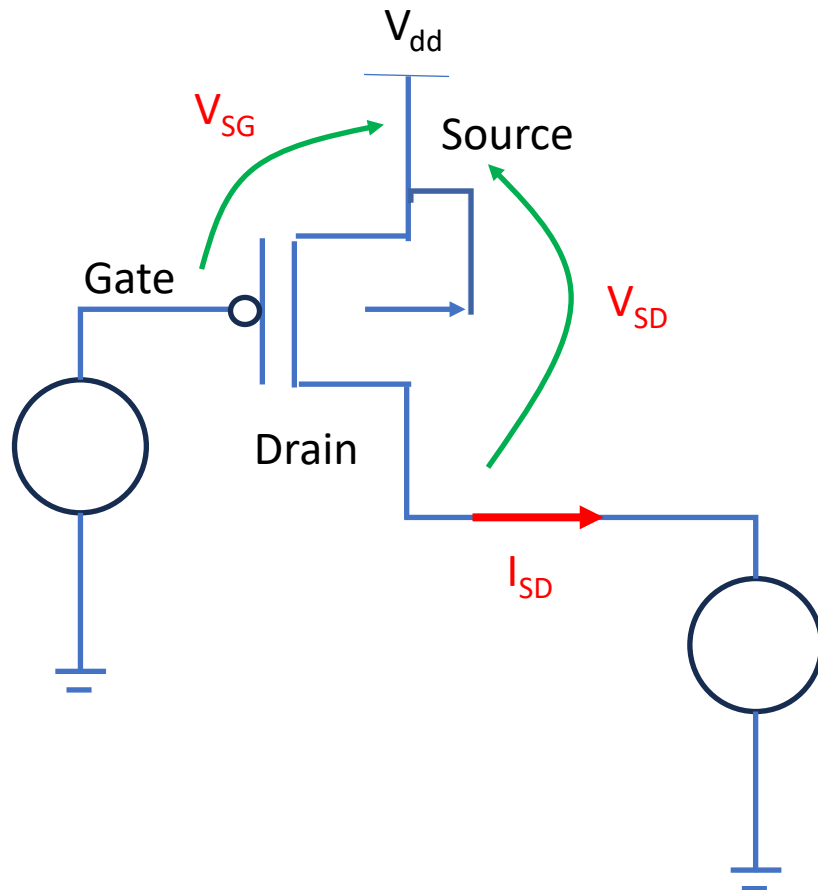
$$I_{DS} = \mu C_{ox} \frac{W}{L} \left[ (V_{GS} - V_T) V_{DS} - \frac{V_{DS}^2}{2} \right]$$

$< 0 !$

$$I_{DS} = \begin{cases} 0 & V_{GS} > V_T \\ < 0 & V_{GS} \leq V_T \end{cases}$$

# pMOS transistor - III

- It has a complementary behaviour with respect to nMOS transistors.

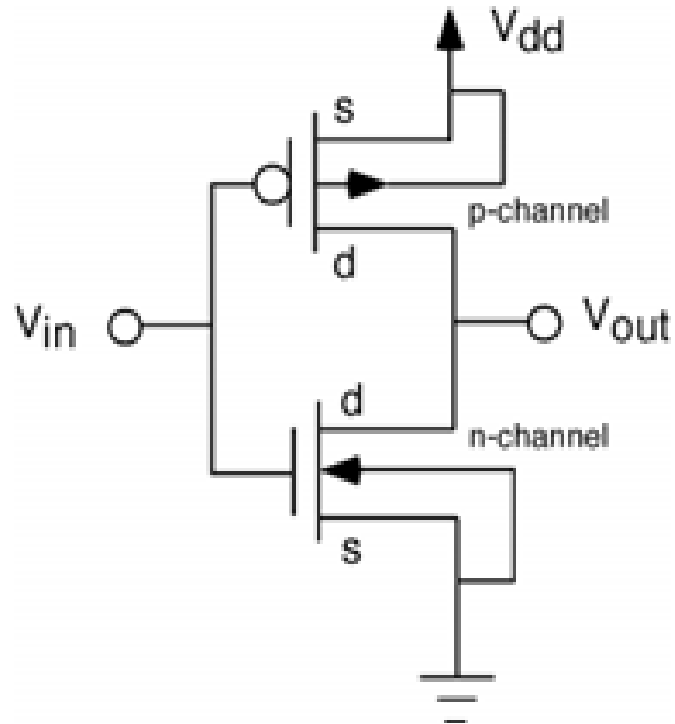


$$I_{SD} = \mu C_{ox} \frac{W}{L} \left[ (V_{SG} - |V_T|) V_{SD} - \frac{V_{SD}^2}{2} \right]$$

$$I_{SD} = \begin{cases} 0 & V_{SG} < |V_T| \\ > 0 & V_{SG} \geq |V_T| \end{cases}$$

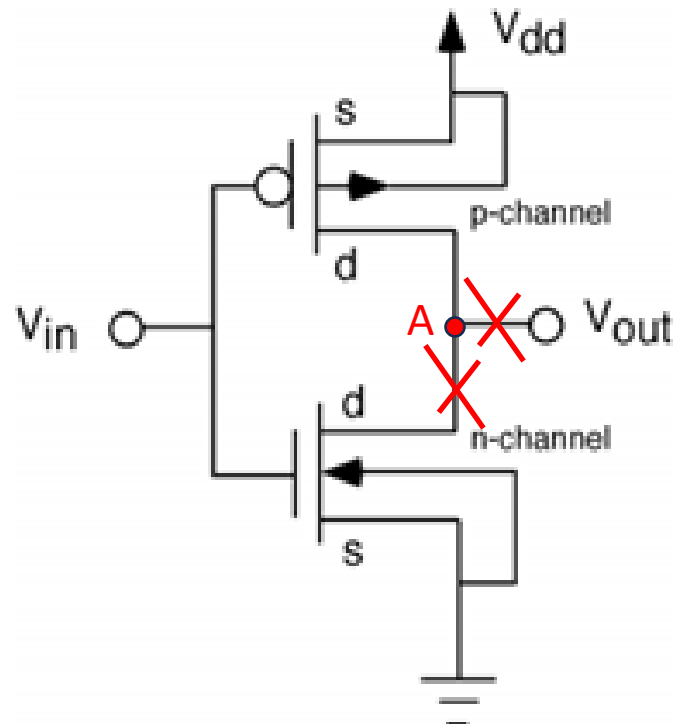
# CMOS Inverter - I

- Use nMOS and pMOS transistors in one circuit
- Example: inverter



# CMOS inverter - II

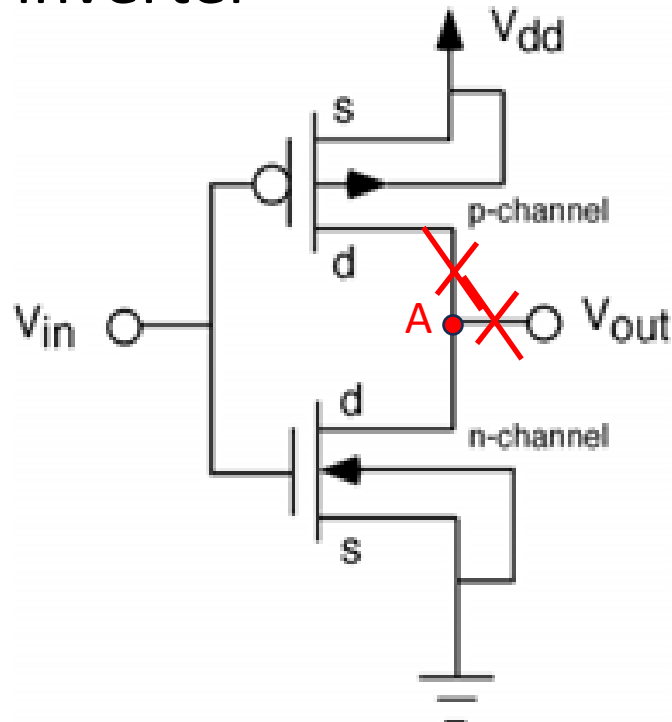
- Use nMOS and pMOS transistors in one circuit
- Example: inverter



1. If  $V_{in}=0$  (gnd – logic '0') the nMOS is off ( $I_{DS}=0$ ), the pMOS is on;
2. KCL at node A says that the current in the pMOS must be zero too. So  $V_{SD}$  of the pMOS is zero and  $V_{out}=V_{dd}$  (logic '1')

# CMOS inverter - III

- Use nMOS and pMOS transistors in one circuit
- Example: inverter

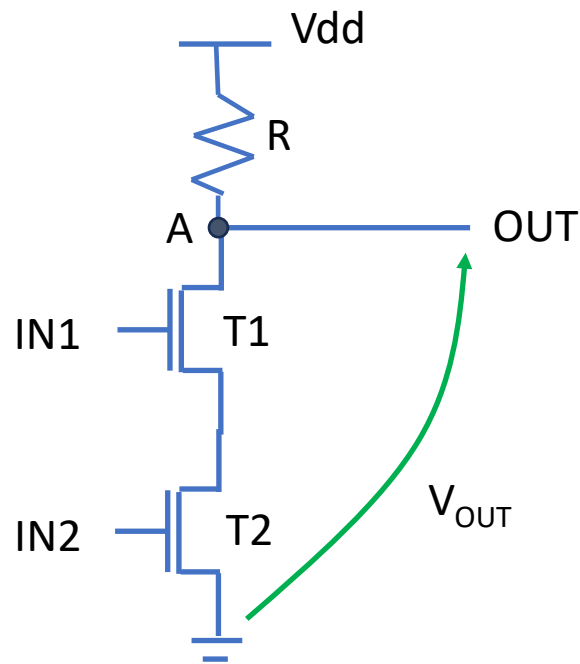


1. If  $V_{in} = V_{dd}$  (logic '1') the nMOS is on, the pMOS is off ( $I_{SD} = 0$ );
2. KCL at node A says that the current in the nMOS must be zero too. So  $V_{DS}$  of the nMOS is zero and  $V_{out} = 0$  (logic '0')



# Other logic functions - I

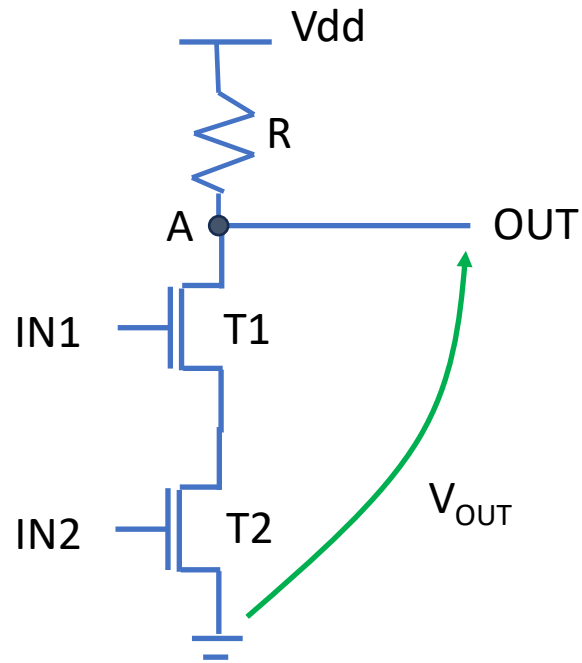
- Using pMOS and nMOS we can easily build NAND and NOR gates.
  - Example:



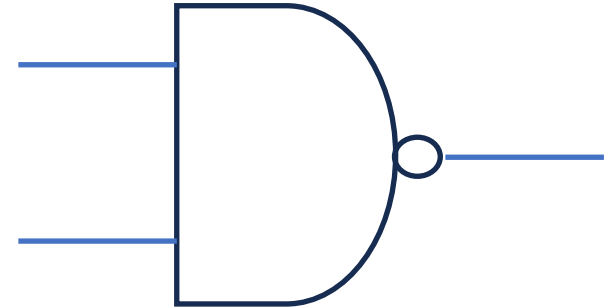
- If  $IN1='1'$  and  $IN2='1'$ , then  $T1$  and  $T2$  are on.
- Thus,  $V_{out} \approx 0$  and so  $OUT='0'$
- If  $IN1='0'$  (or  $IN2='0'$ ), then  $I_{DS1}=0$  (or  $I_{DS2}=0$ ). Thus, no current flows in the branch with  $T1$  and  $T2$
- KCL at node  $A$  says that no current flows in  $R$ , so no voltage drop across  $R$ .
- As a consequence,  $V_{out}=V_{dd}$  and  $OUT='1'$

IN1	IN2	OUT
0	0	1
0	1	1
1	0	1
1	1	0

# Other logic functions - II

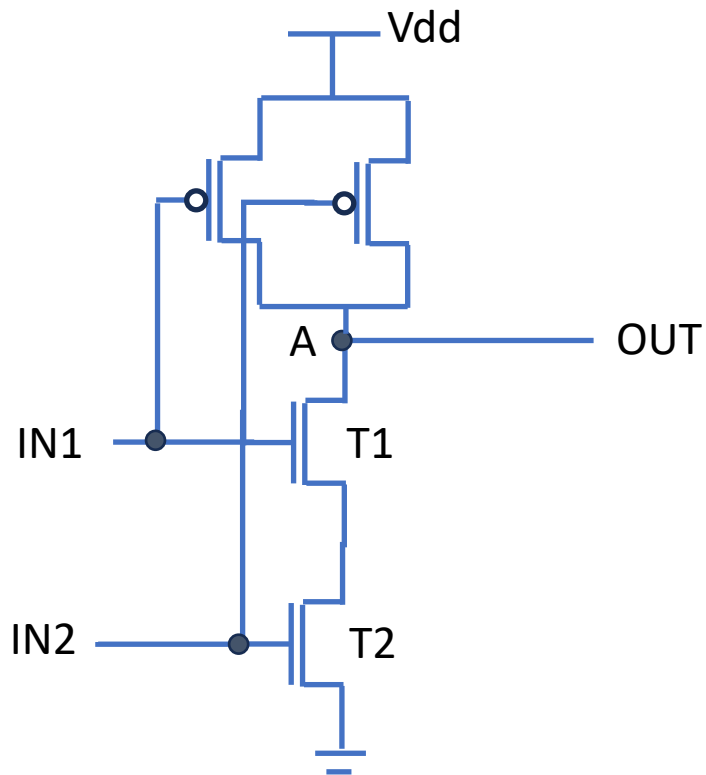


IN1	IN2	OUT
0	0	1
0	1	1
1	0	1
1	1	0

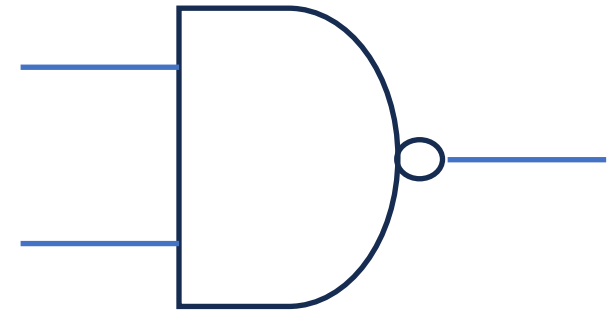


# Other logic functions - III

- Exploiting pMOS/nMOS complementary behaviour, we obtain



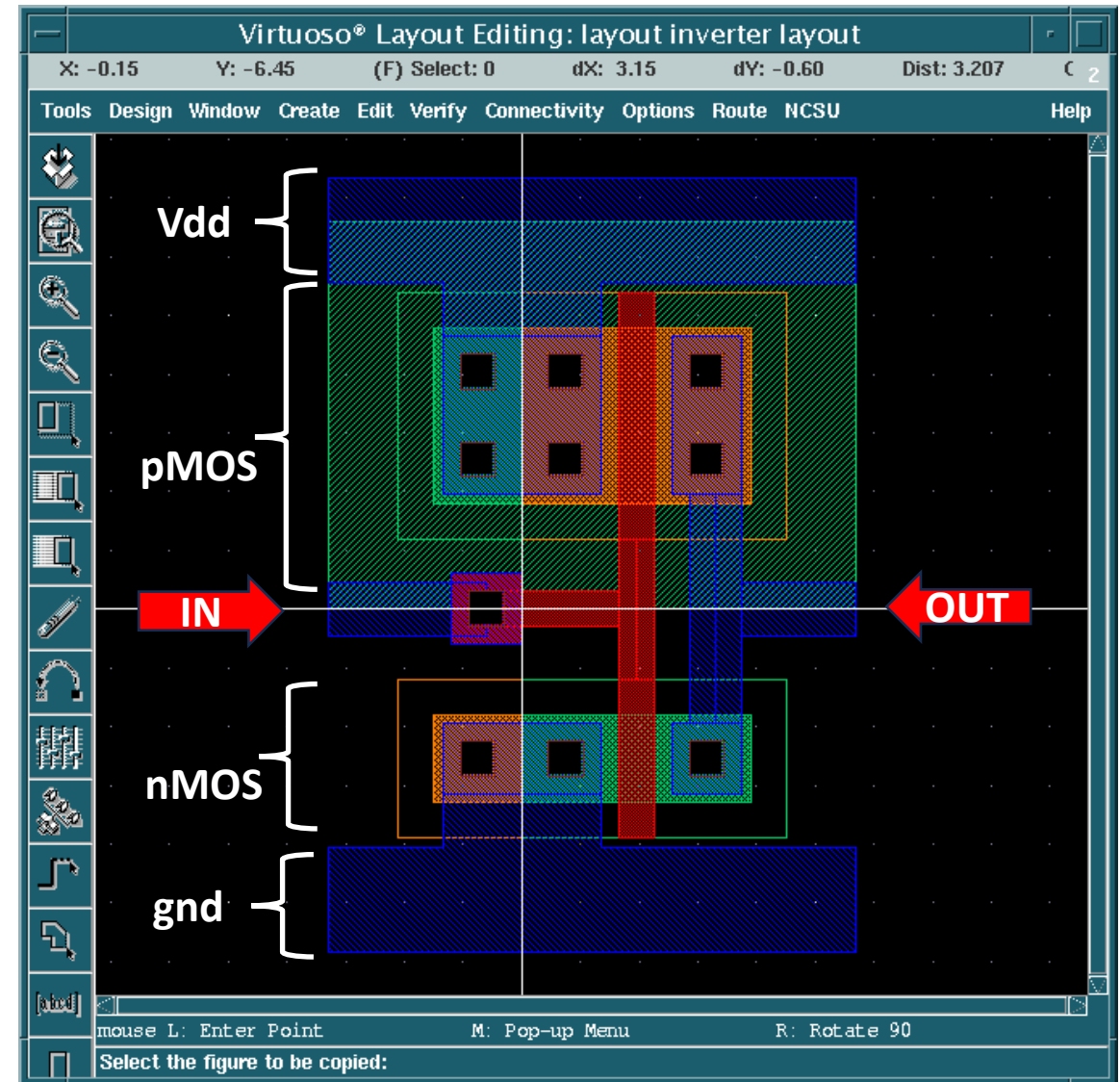
IN1	IN2	OUT
0	0	1
0	1	1
1	0	1
1	1	0



# CMOS logic

- We can extend the NAND example to other gates (NOR, ...)
- The nMOS branch and pMOS branch work in complementary mode to implement a Complementary MOS (CMOS) logic.
- Once we know the logic function we can design the layout of the corresponding circuit.

# Example: CMOS inverter layout



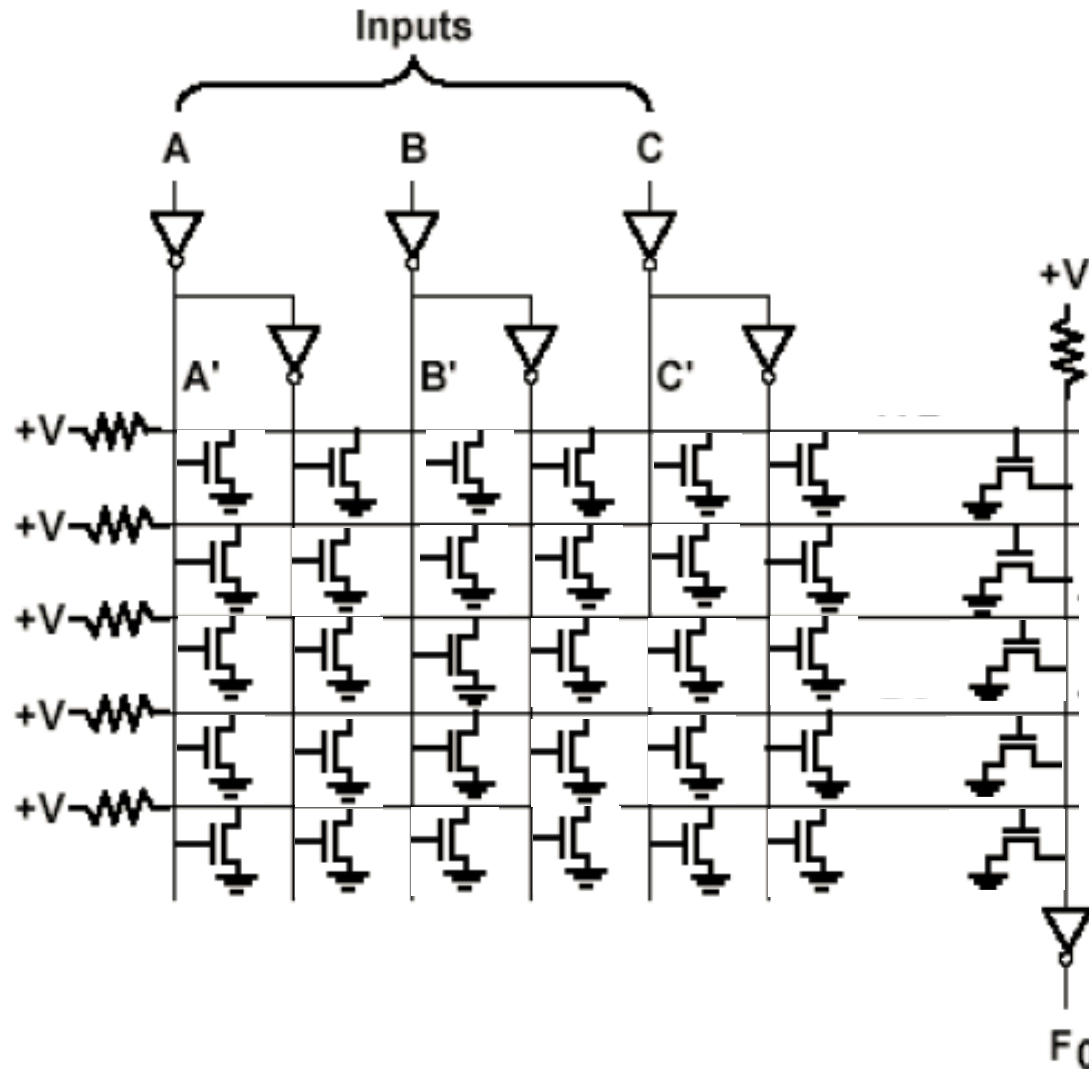
# What is required ?

- Process Design Kit (PDK): the set of layers and rules to draw a layout
  - PDKs usually prepared by silicon foundries;
  - Access requires signing Non-Disclosure-Agreements (NDAs);
  - Some free PDKs exist, e.g. SkyWater 130.
- A tool to design and simulate circuits/gates exploiting a PDK.
  - Tools used at industrial level licensed paying fees.
  - Some free tools exist, e.g. Magic and kLayout.

# VLSI design methodologies

- The methodology we saw so far:
  - Contains the basis steps to fully design and optimize your circuit from scratch
  - Is typical of Application-Specific Integrated Circuits (ASICs)
- However, with few transistors one can build NAND and NOR gates
  - Is its enough to build any combinational logic function !
  - Instead of designing all the transistors from scratch rely on pre-built arrays.
  - Programming the connection obtain arbitrary functions
  - Typical approach to build programmable devices (PAL, PLA, CPLD, FPGA)

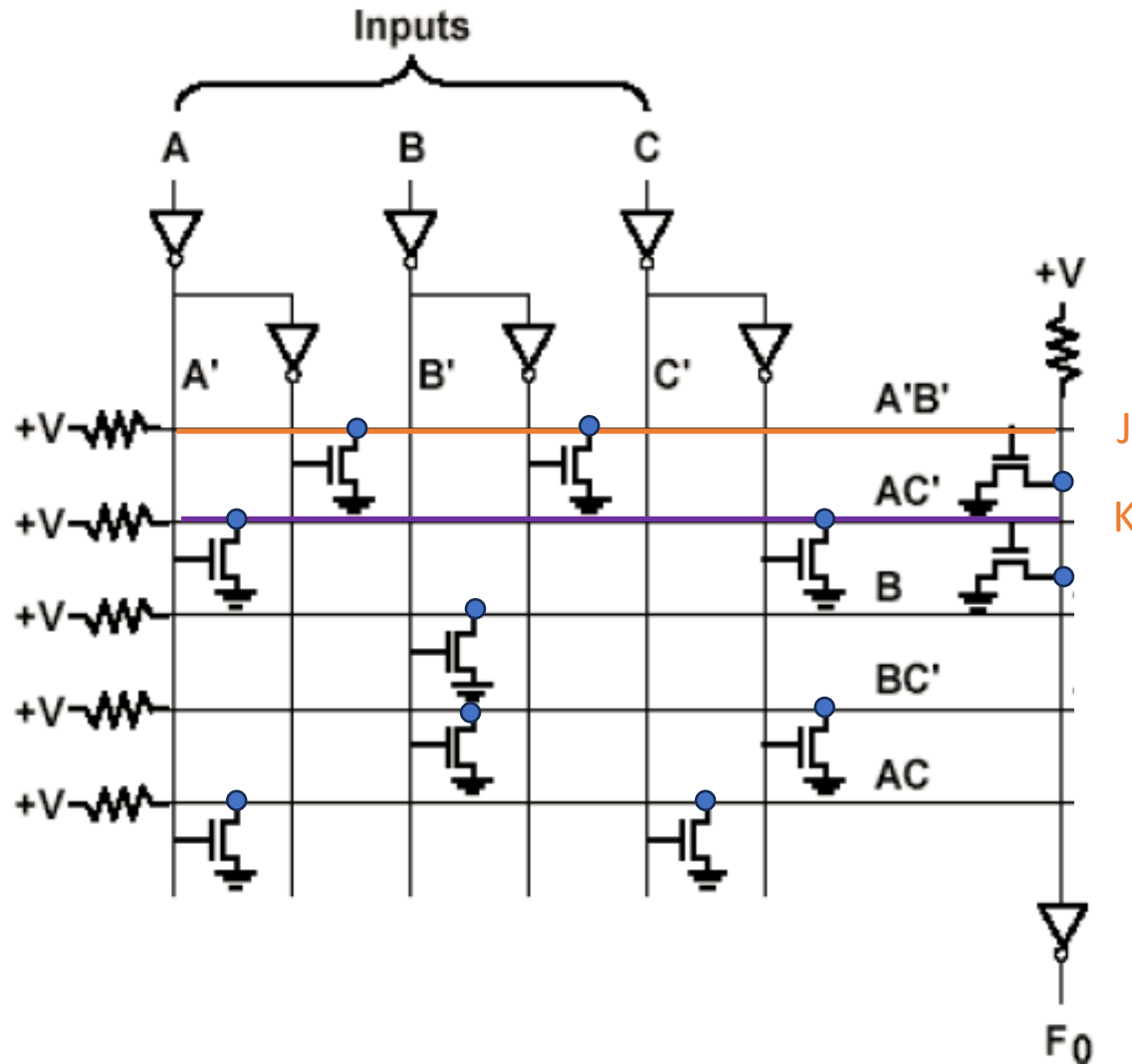
# Example: programmable device - I



$$F_0 = \overline{A} \cdot \overline{B} + A \cdot \overline{C}$$



# Example: programmable device - II



$$J = \overline{A + B} = \overline{A} \cdot \overline{B}$$

$$K = \overline{\overline{A} + C} = A \cdot \overline{C}$$

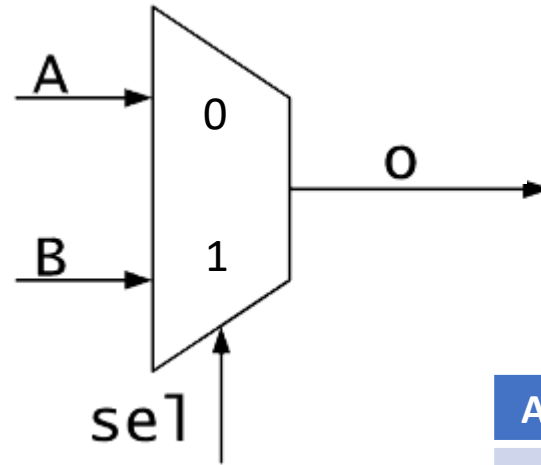
$$F_0 = J + K = \overline{A} \cdot \overline{B} + A \cdot \overline{C}$$

# Digital electronics

- Combinational circuits
  - Circuits with no memory:  $O_t = f(I_t)$
  - Examples: gates (NOT, NAND, AND, ...), selectors (multiplexers), arithmetic operations, ...
- Sequential circuits
  - Circuits with memory behaviour:  $O_t = g(I_t, O_{t-k})$ 
    - Asynchronous: the output can change in any time slot, without any reference
    - Synchronous: output changes are synchronized by a reference signal, usually referred to as clock (square wave with duty cycle 50%)
      - Level triggered: latch-like behaviour (50% transparency phase - 50% memory phase)
      - Edge triggered: flip-flop-like behaviour (instantaneous transparency phase – long memory phase)
        - Positive edge triggered (rising edge)
        - Negative edge triggered (falling edge)
        - Double Data Rate (both rising and falling)

# Combinational circuits example

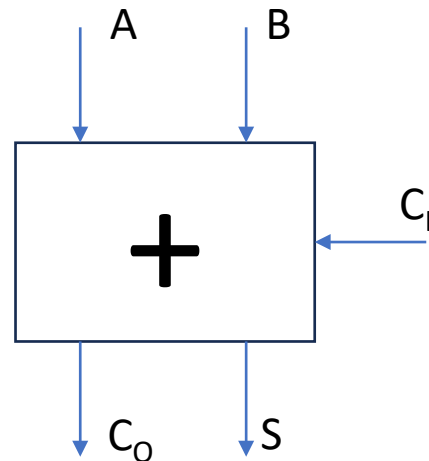
- Multiplexer



A	B	sel	O
-	-	0	A
-	-	1	B

$$O = A \cdot \overline{\text{sel}} + B \cdot \text{sel}$$

- Full adder



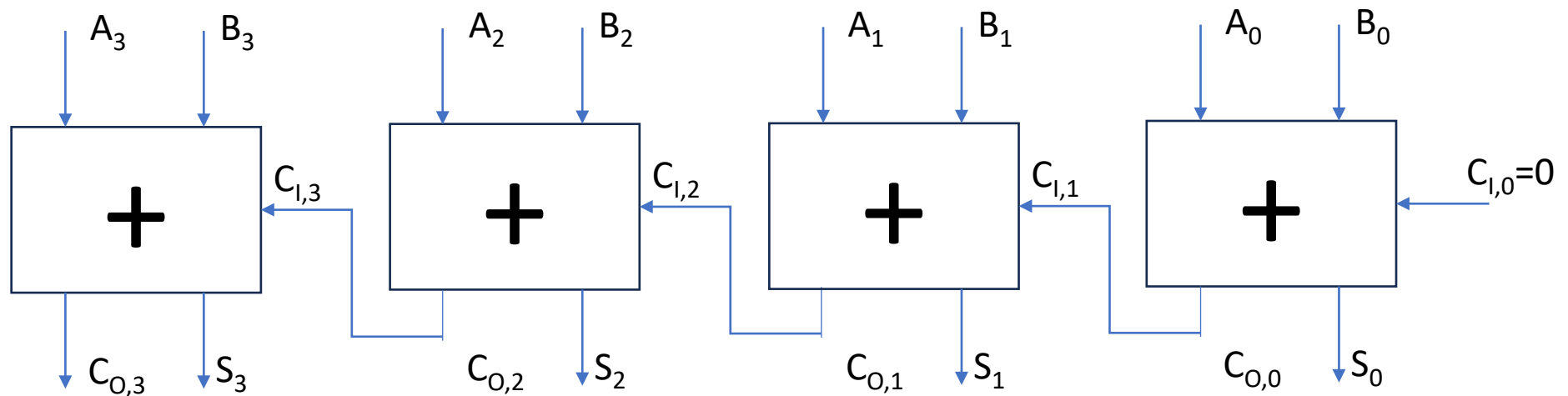
A	B	C <sub>i</sub>	S	C <sub>o</sub>
0	0	0	0	0
0	0	1	1	0
0	1	0	1	0
0	1	1	0	1
1	0	0	1	0
1	0	1	0	1
1	1	0	0	1
1	1	1	1	1

$$S = A \oplus B \oplus C_i$$

$$C_o = A \cdot B + A \cdot C_i + B \cdot C_i$$

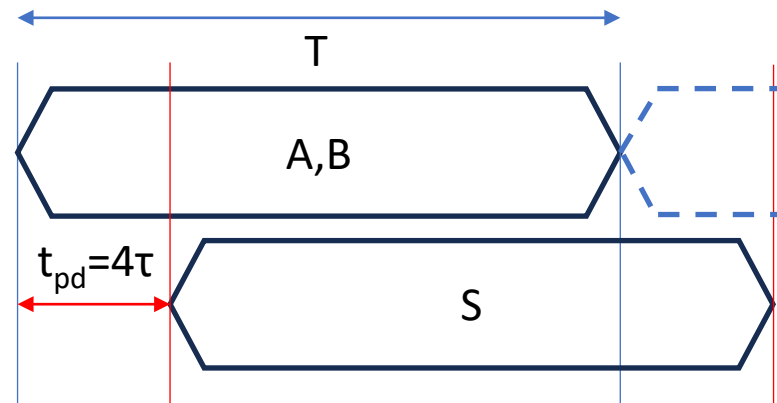
# More on combinational circuits

- Important parameter: combinational delay
  - The output is not updated instantaneously
  - There is a delay between changes in the input (triggering a change in the output) and actual output update
- Example:
  - 4bit adder



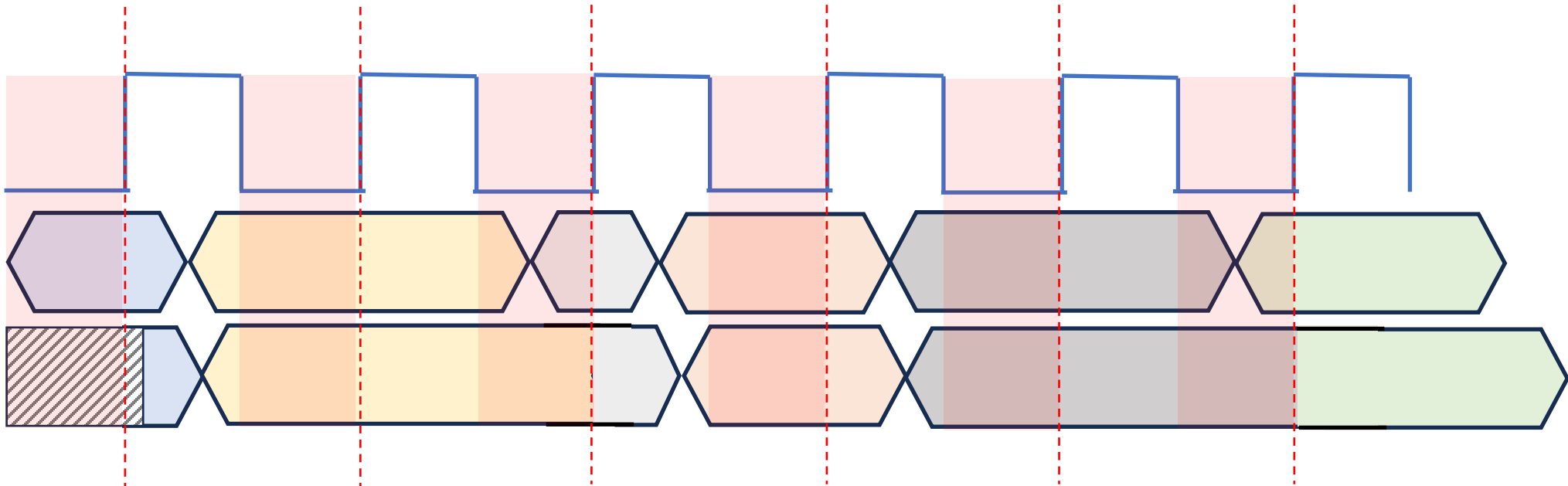
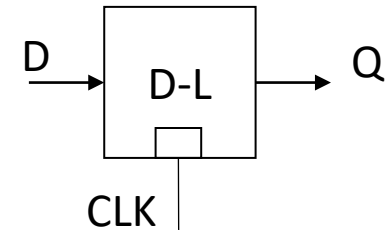
# Combinational delay

- Assume one full adder introduces a propagation delay  $\tau$ 
  - $S_3$  delay is  $4\tau$
  - Cascading combinational blocks increases the propagation delay ( $t_{pd}$ )
- If data change at a certain rate  $T$ , the maximum combinational delay must guarantee correct results:  $t_{pd} < T$



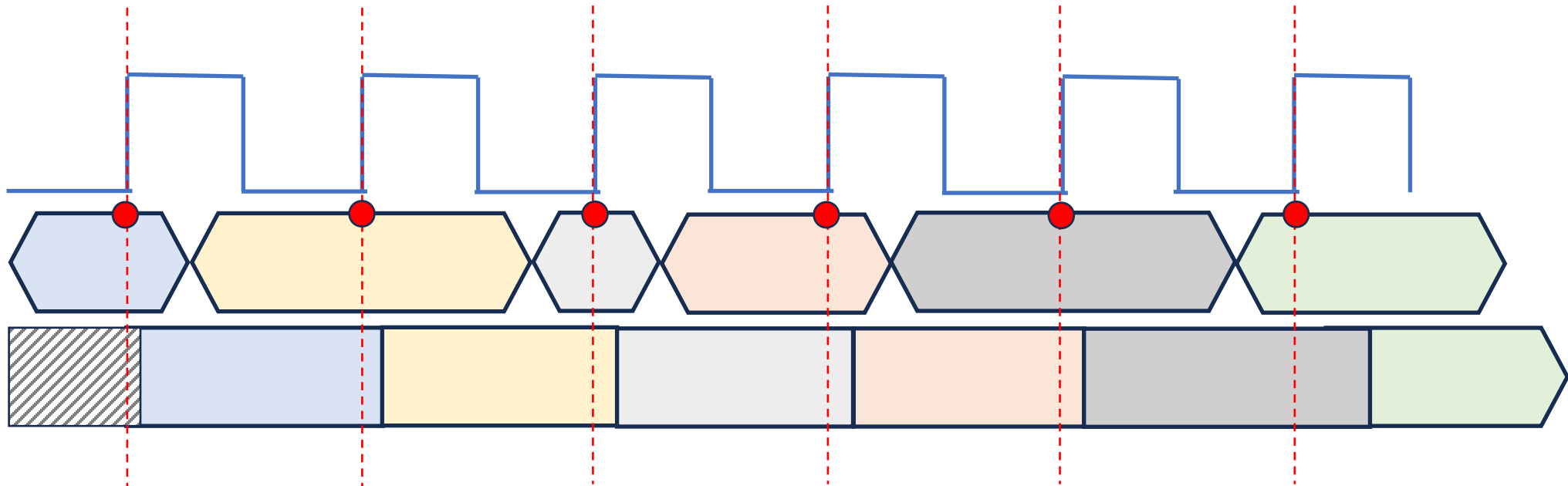
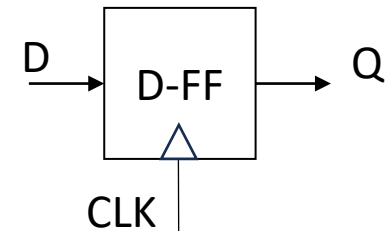
# Sequential circuits - I

- Level triggered (Latch-like)
  - Simplest example: D-type latch
    - When the clock is low → Memory
    - When the clock is high → Transparency



# Sequential circuits - II

- Positive edge triggered (Flip-Flop-like)
  - Simplest example: D-type Flip-Flop
    - Always in Memory
    - Except on the rising edge of the clock → Transparency

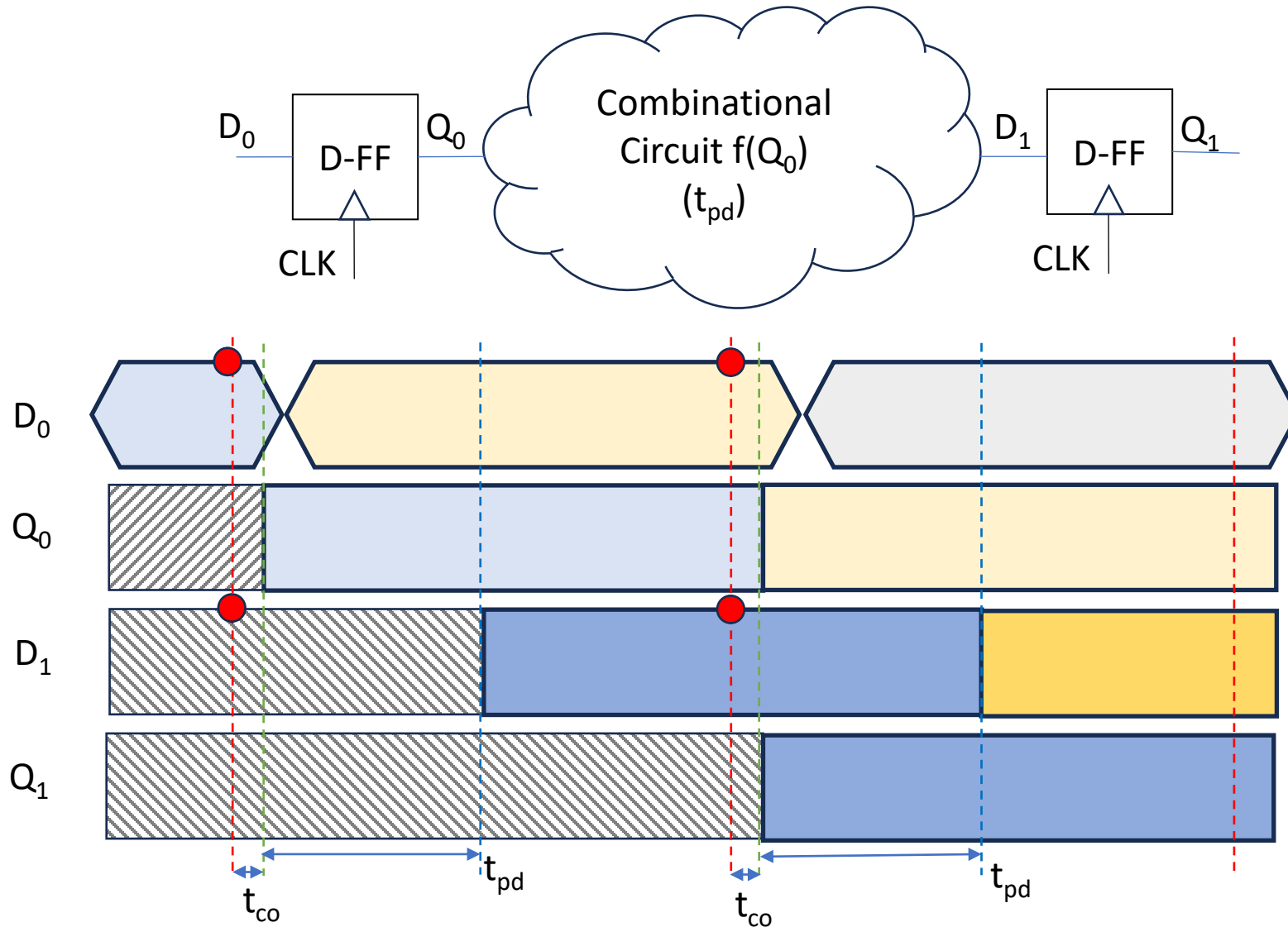


# Sequential circuits - II

- Level triggered Vs positive edge triggered
  - Level triggered elements have a direct path between input and output during transparency phase
  - Cascade of level triggered elements in the transparency phase behaves as a chain of combinational circuits (potentially long  $t_{pd}$ )
    - It can be avoided cascading sequences of positive/negative level triggered elements
      - Complex especially if there is a feedback
- Positive edge triggered elements can be cascaded (no effect on the delay)
  - Increasing latency
  - Easy calculation of the maximum speed of the circuit.

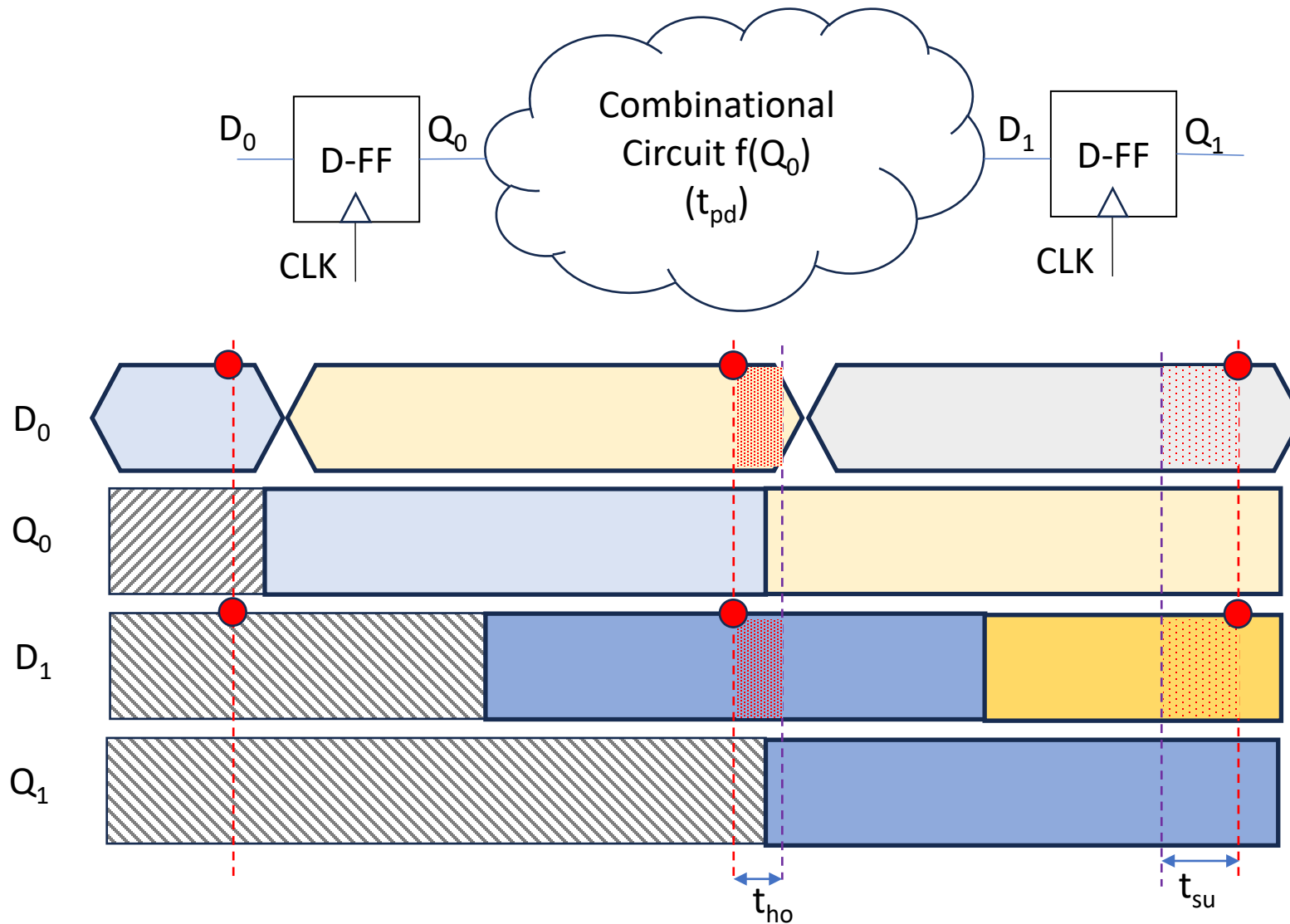


# Example: circuit with FFs - I



- $t_{co} \rightarrow$  Clock-to-output delay

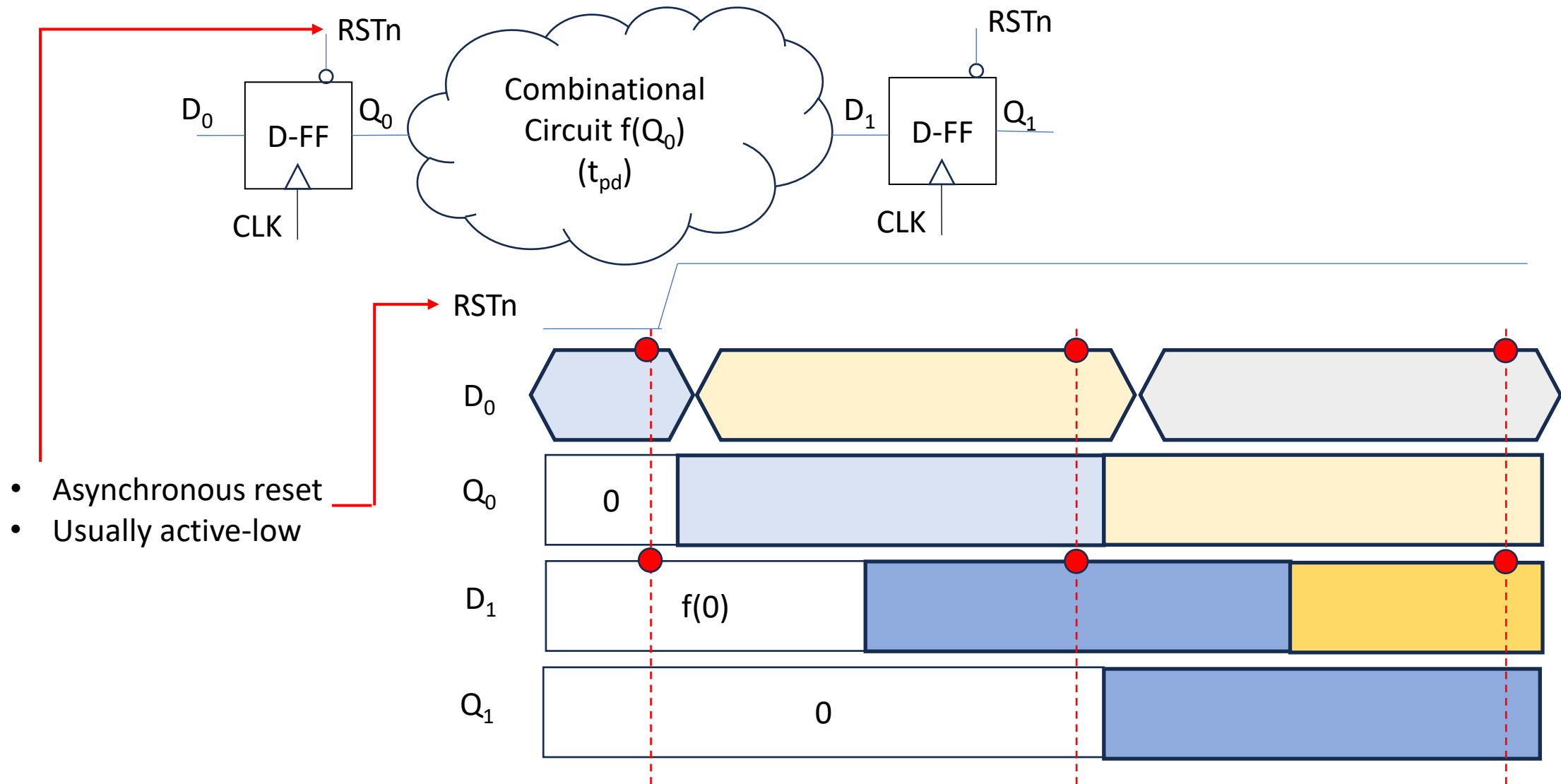
# Example: circuit with FFs - II



- $t_{co} \rightarrow$  Clock-to-output delay
- $t_{su} \rightarrow$  Setup time
- $t_{ho} \rightarrow$  Hold time

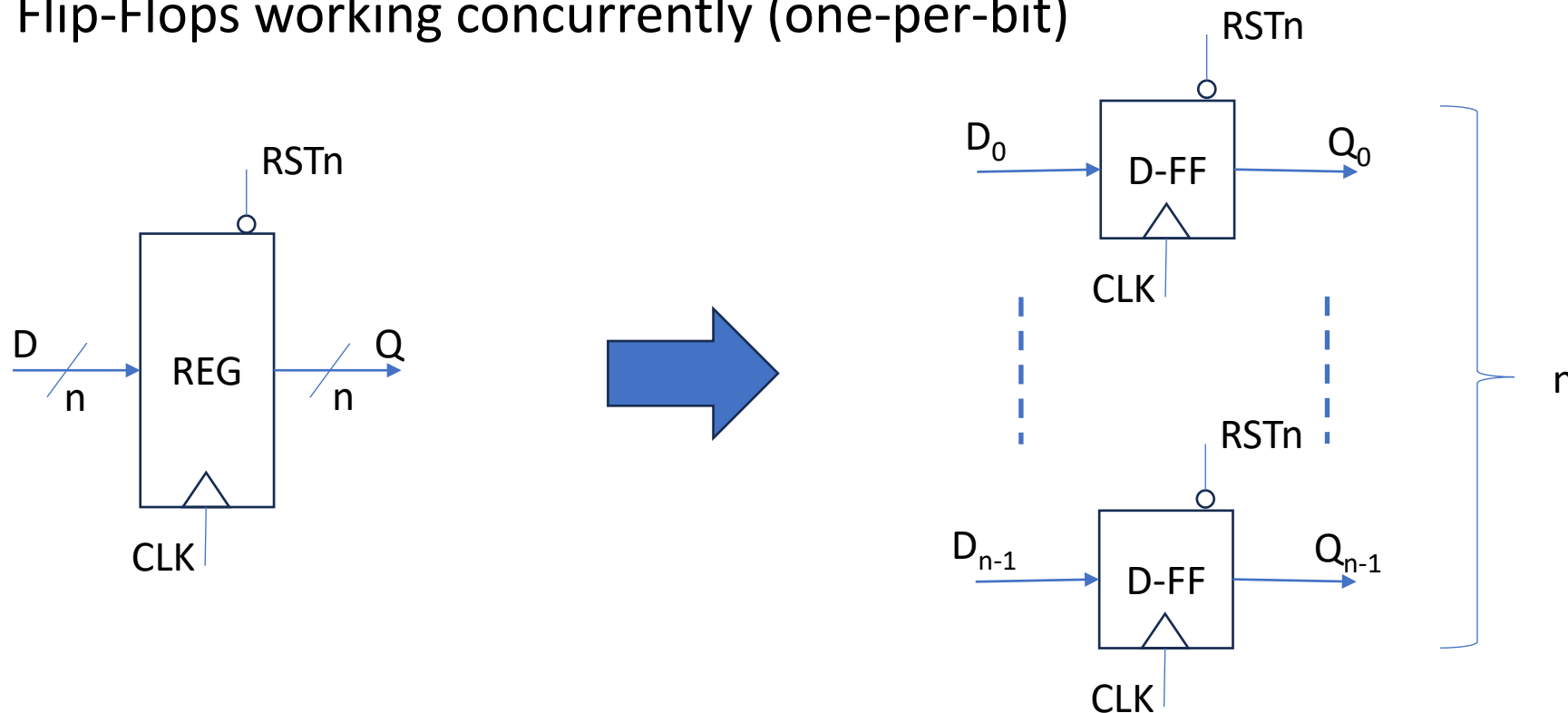
$$T_{clk} \geq t_{co} + t_{pd} + t_{su}$$
$$t_{co} + t_{pd} \geq t_{ho}$$

# Example: circuit with FFs - III



# From Flip-Flops to registers

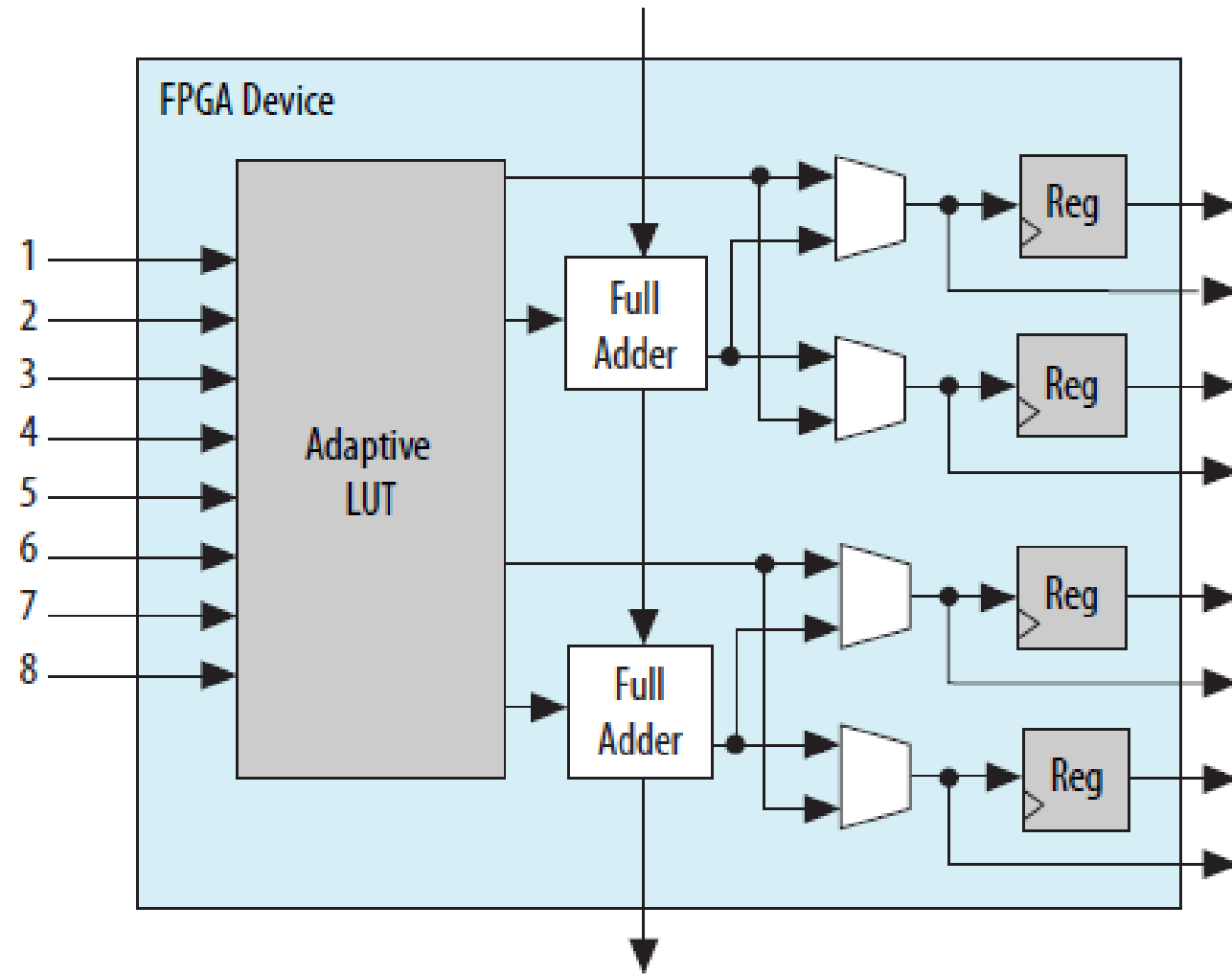
- Flip-Flop  $\rightarrow$  1-bit-data
- Register (parallel register)  $\rightarrow$  n-bit-data
  - n Flip-Flops working concurrently (one-per-bit)



# VLSI design methodologies (continue)

- The methodology we saw for designing transistors (W/L) can still be applied ... but the number of transistor has increased.
- Adding sequential circuits to a programmable combinational structure increases the potential of the programmable device.
  - Modern programmable devices (FPGAs) replaced the NAND/NOR programmable combinational structure with Look-Up Tables (LUTs)

# Example: basic cell of an Intel-Altera FPGA

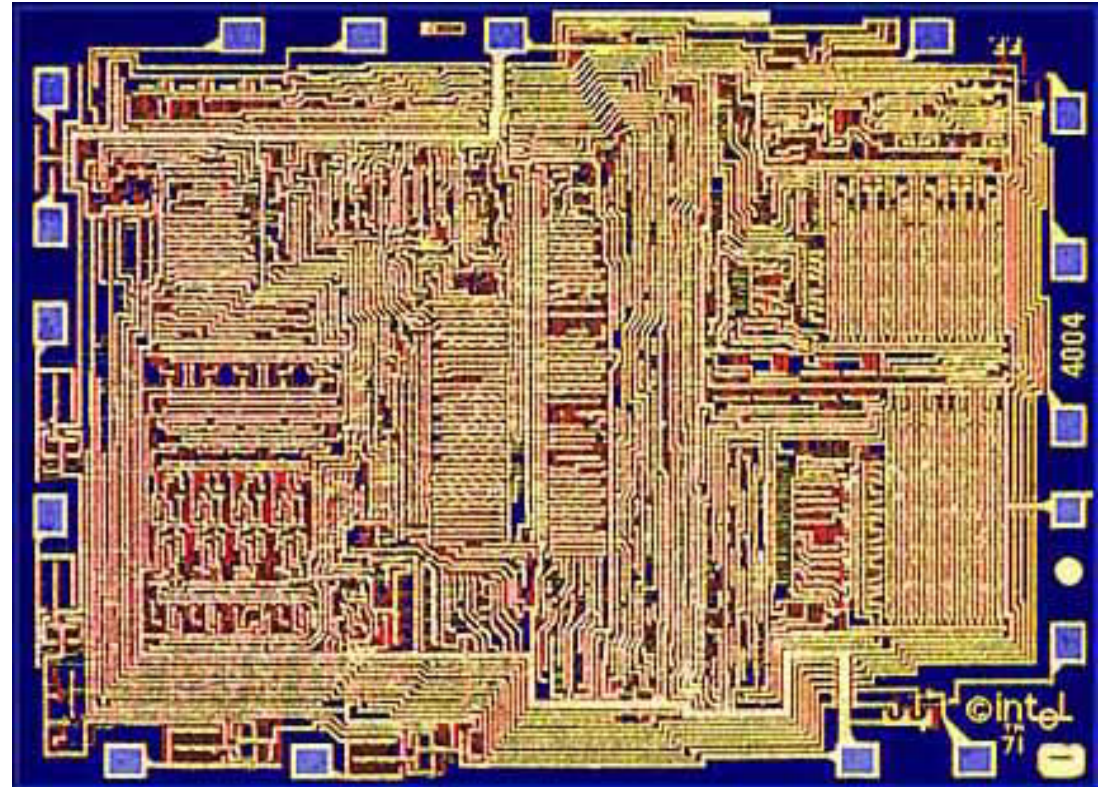


# VLSI design styles

- Custom Design
- Semi-Custom Design
- Programmable Logic Devices (PLDs)

# Custom Design

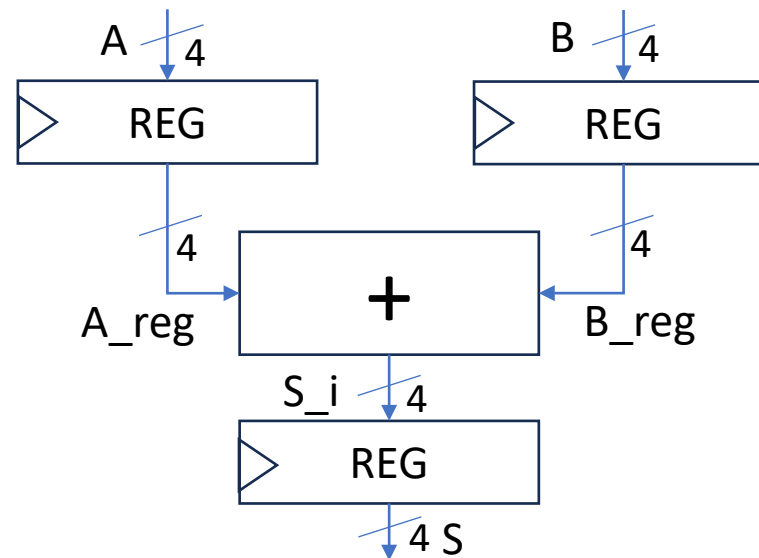
- Extension of the methodology seen so far (W/L).
- Viable for small designs or critical parts.
- Example: INTEL 4004 (1971)



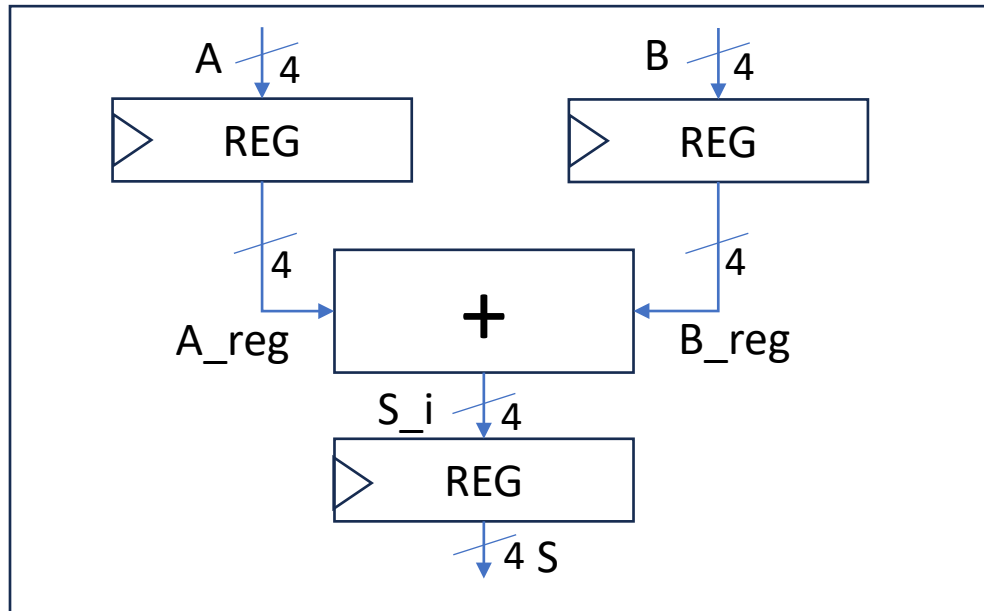


# Semicustom design

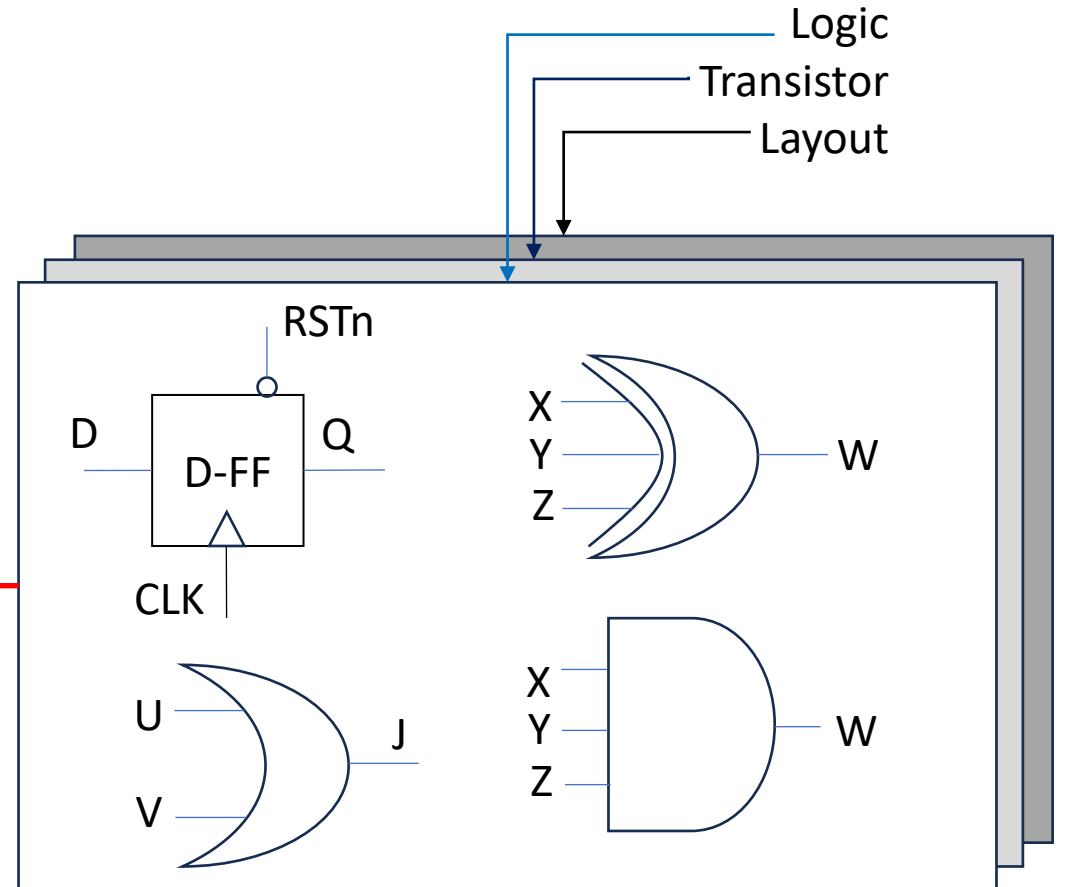
- For mid/complex designs:
  - Rely on a library of cells already made by someone else (silicon foundry)
  - Use them as bricks to build the circuit.
  - Example:
    - 4 bit adder with input and output registers



# Example - I



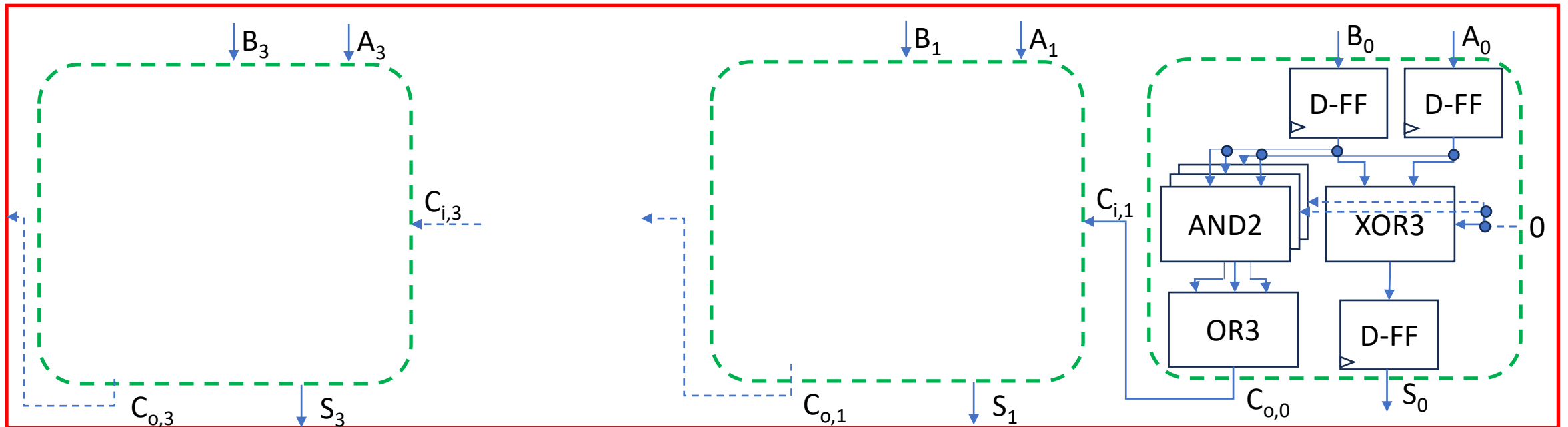
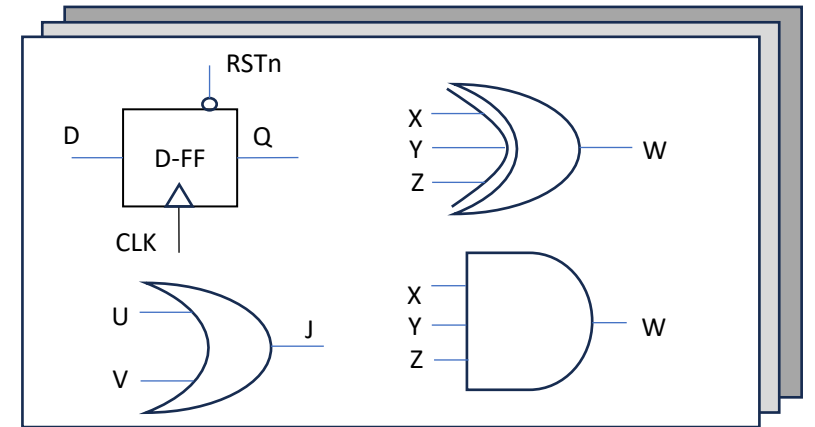
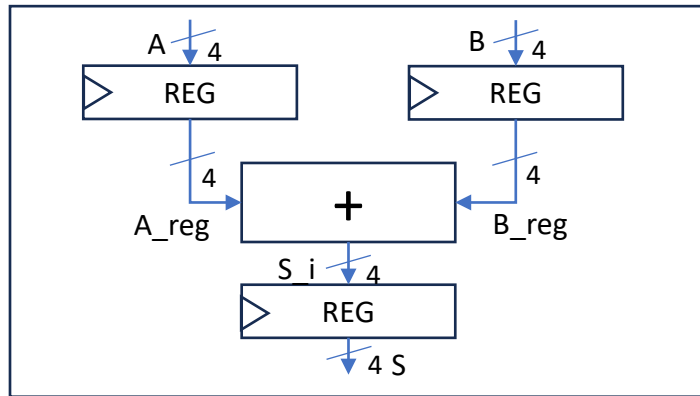
Register Transfer Level (RTL) description



Library of cells

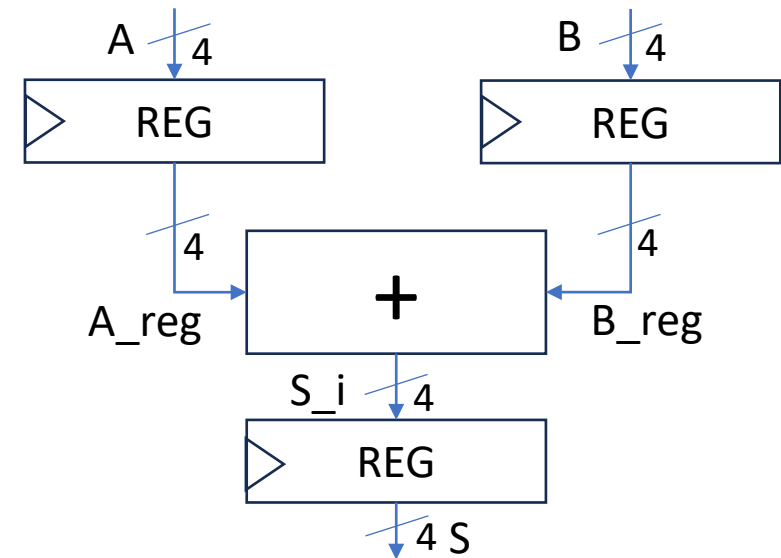
Netlist

# Example - II

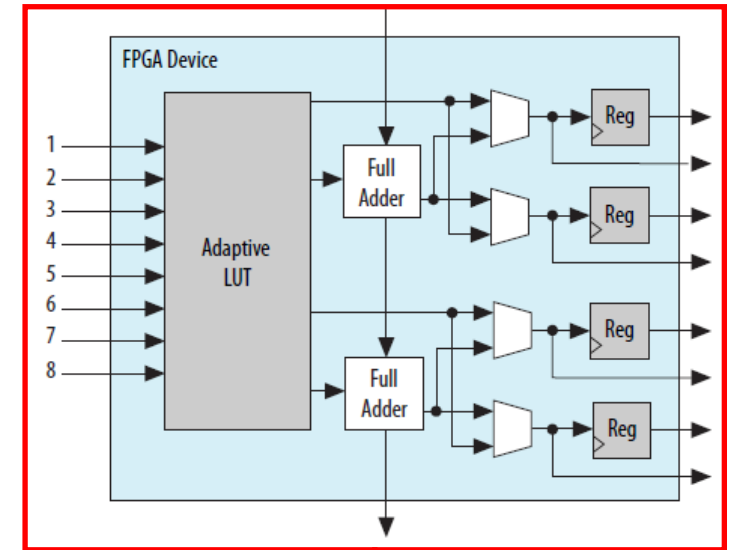
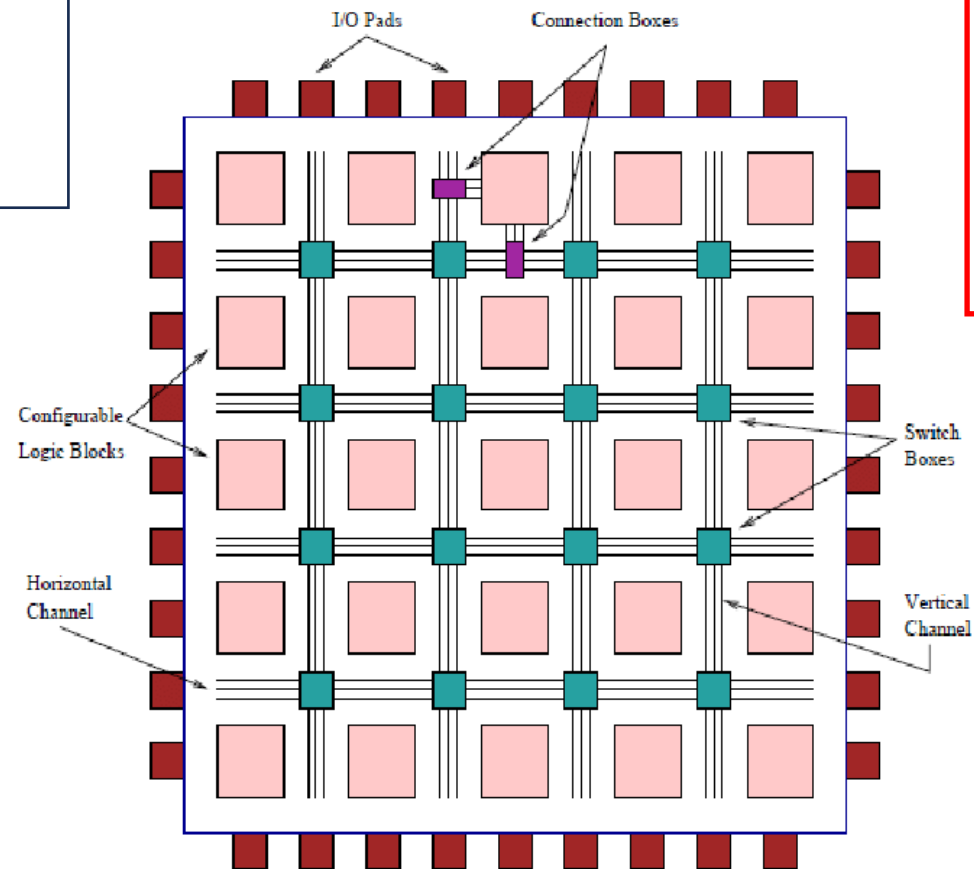
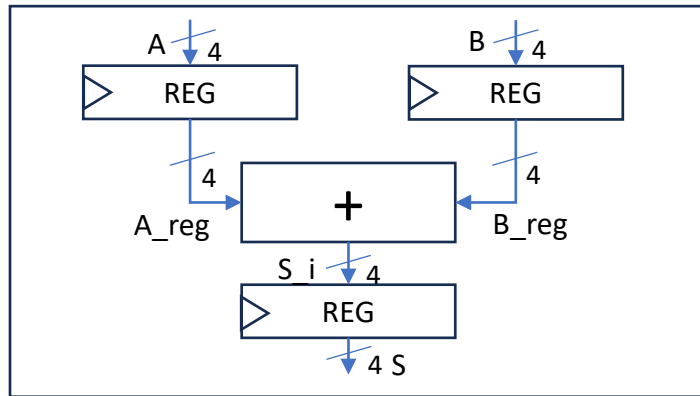


# Programmable logic devices

- For simple to complex designs:
  - Rely on an array of programmable cells already made by someone else (PLD vendor)
  - Use them as bricks to build the circuit.
  - Example:
    - 4 bit adder with input and output registers

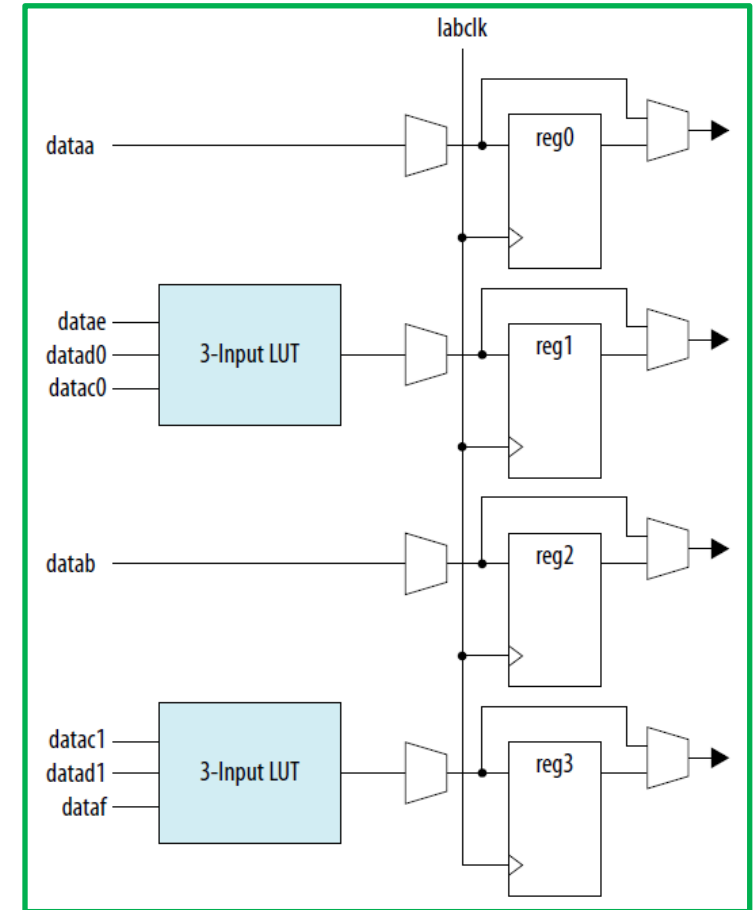
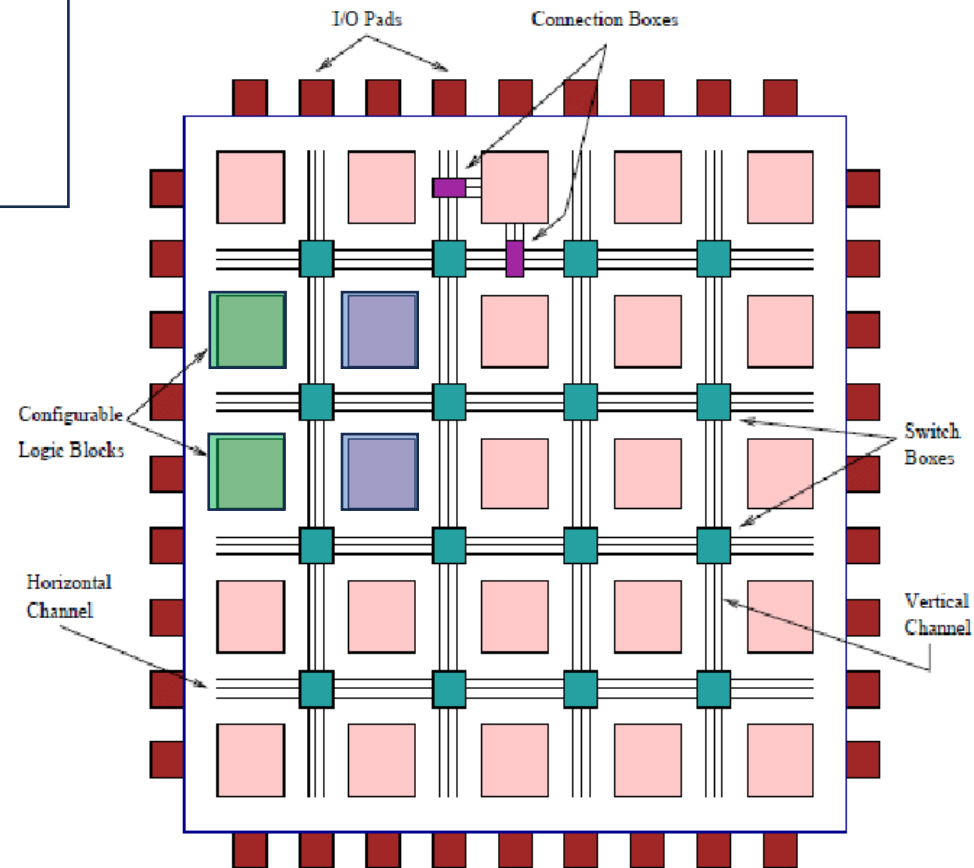
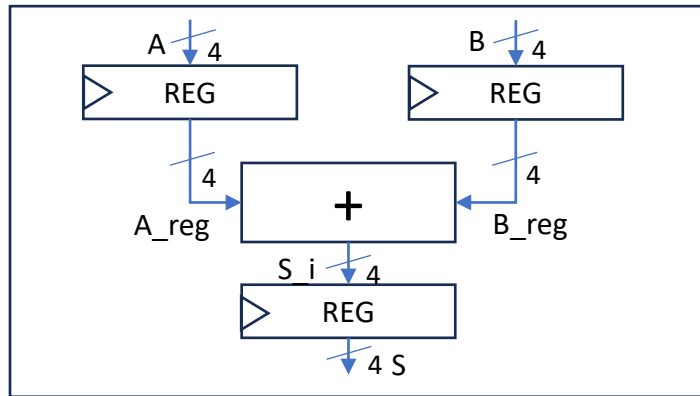


# Example - I

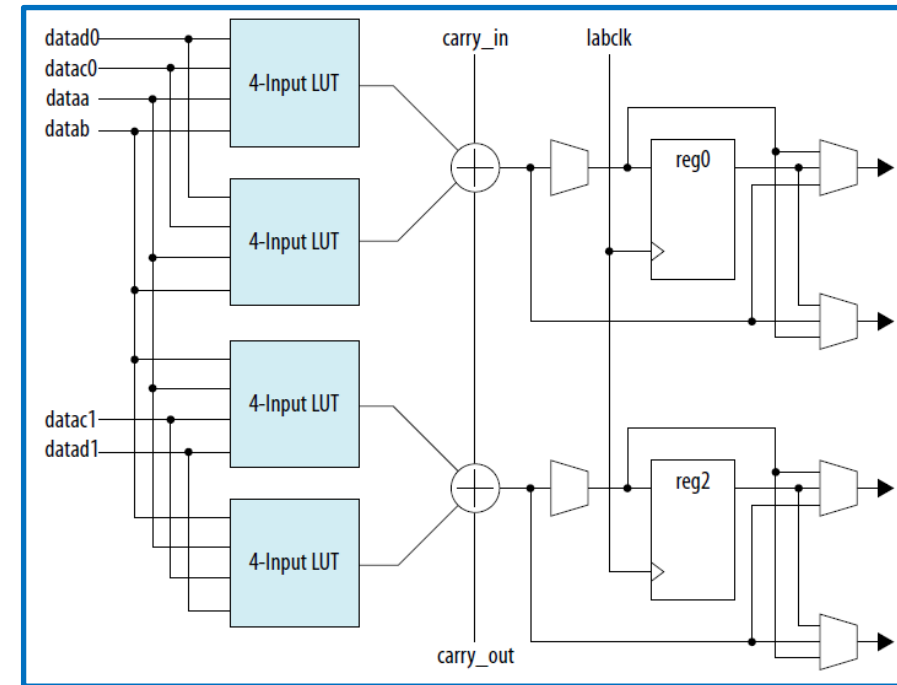
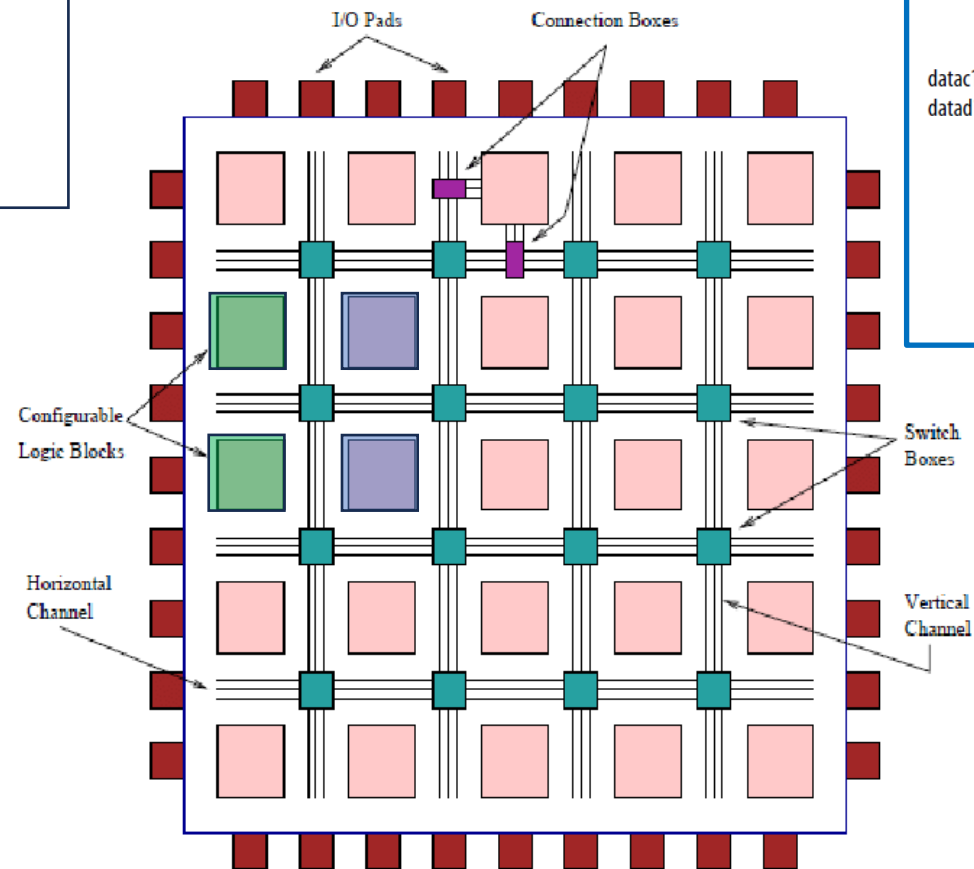
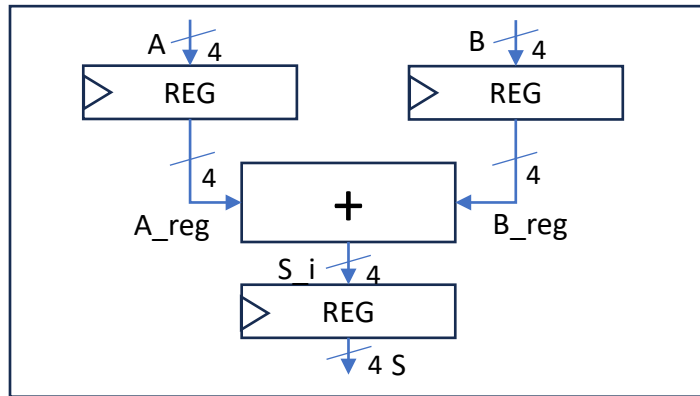


Can be configured in different modes

# Example - II



# Example - III



# Design flow

- If the circuit complexity increases, manually translate RTL to logic becomes impossible !
- Exploit Computer Aided Design (CAD) instruments: logic synthesizers
- Elements:
  - RTL description
  - Technology information (standard cells or PLD cells)
  - Constraints (area, timing, power)

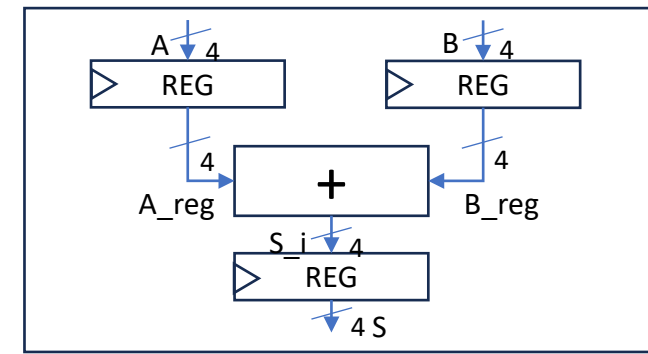


# RTL description

- Circuit description via a Hardware Description Language (HDL)
  - VHDL
  - Verilog/SystemVerilog
- Inspired by object oriented programming languages, but designed for hardware description.
- Clear separation between interface and implementation

# Interface

- Name the element and list signals, directions and types



```
entity add4 is
  port (
    A    : in  std_logic_vector(3 downto 0);
    B    : in  std_logic_vector(3 downto 0);
    CLK  : in  std_logic;
    S    : out std_logic_vector(3 downto 0));
end entity add4;
```

VHDL

```
module add4 (input [3:0] A,
             input [3:0] B,
             input CLK,
             output reg [3:0] S);

  /* implementation */

endmodule
```

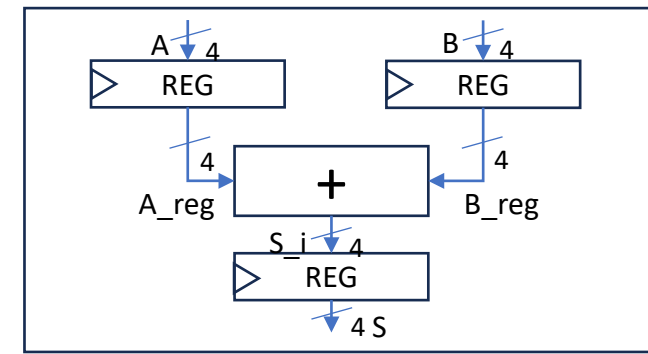
Verilog

# Implementation

- Contains only three possible elements (acting concurrently):
  - Components
    - Hierarchical design
  - Processes
    - To model sequential elements
    - To model (mainly) combinational decoders
  - Assignments
    - To model simple combinational logic (mainly arithmetic and logic functions)

# VHDL

- Use of process and assignment



```
architecture beh of add4 is
```

```
    signal A_reg : std_logic_vector(3 downto 0);  
    signal B_reg : std_logic_vector(3 downto 0);  
    signal S_i : std_logic_vector(3 downto 0);
```

```
begin -- architecture beh
```

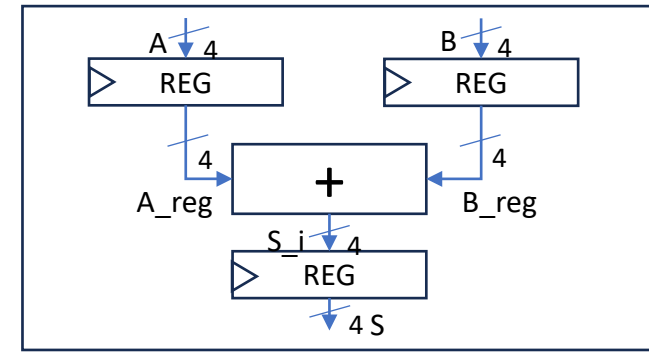
```
    process (CLK) is  
    begin -- process  
        if CLK'event and CLK = '1' then -- rising clock edge  
            A_reg <= A;  
            B_reg <= B;  
            S_i <= S_i;  
        end if;  
    end process;
```

```
    S_i <= A_reg + B_reg;
```

```
end architecture beh;
```

# Verilog

- Use of process and assignment



```
always @ (posedge CLK) begin
    A_reg <= A;
    B_reg <= B;
    S <= S_i;
end

assign S_i = A_reg + B_reg;
```

# Design flow (continue)

- Elements:
  - ✓ RTL description
  - ✓ Technology information (standard cells or PLD cells)
    - Standard cells
      - usually prepared by silicon foundries;
      - Access requires signing Non-Disclosure-Agreements (NDAs);
      - Some free sets of standard cells exist, e.g. SkyWater 130.
    - PLD
      - vendors provide just enough details to developers
      - Simpler/older devices often for free
      - Complex/modern devices require fees
  - ✓ Constraints (area, timing, power)
    - Imposed by the designer based on the application requirements
    - Example, Synopsys Design Constraints (sdc)  
`create_clock -name MYCLK -period 3.5 CLK`

# Logic synthesizers

- Tools used at industrial level licensed paying fees.
- ASIC
  - Some free tools exist, e.g. YOSYS
- PLD
  - Development tools are usually offered for free with limited features
  - E.g.
    - Vivado/Vitis by AMD/Xilinx
    - Quartus Prime by Intel/Altera
    - ...

# Logic synthesis - I

- Provide the tool with area, timing, power information about the cells.
- Example, liberty file:

```
library ("library_name") {  
    ...  
    /* Units */  
    time_unit : "1ns";  
    voltage_unit : "1V";  
    leakage_power_unit : "1nW";  
    current_unit : "1mA";  
    ...  
    cell ("nand2") {  
        area : 3.7536000000;  
        ...  
        /* timing and power data */  
        ...  
    }  
}
```



# Logic synthesis - II

1. Read area/timing/power cells file
2. Read the HDL description and map it to a generic RTL description.
3. Read constraints.
4. Map/optimize the RTL description on the available cells
5. Write the resulting netlist

# Example

```
module add4 (A, B, CLK, S);  
    input [3:0] A;  
    input [3:0] B;  
    input CLK;  
    output reg [3:0] S;  
    wire n0;  
    wire n1;  
    wire n2;  
  
    dff i0 (  
        .CLK(CLK),  
        .D(A[0]),  
        .Q(n0));  
  
    dff i1 (  
        .CLK(CLK),  
        .D(B[0]),  
        .Q(n1));
```

```
xor2 i2 (  
    .A(n0),  
    .B(n1),  
    .X(n2));  
  
dff i3 (  
    .CLK(CLK),  
    .D(n2),  
    .Q(S[0]));  
  
...  
  
endmodule
```

# Netlist to layout ?

- The netlist contains the list of required cells and how they are connected together.
- Given the constraints and the geometrical details of the cells (Library Exchange Format - LEF file), one can place and connect (route) them.
- Tools for Place & Route: the ones used at industrial level licensed paying fees.
  - ASIC
    - Some free tools exist, e.g. OPENROAD
  - PLD
    - Development tools are usually offered for free with limited features
      - Vivado/Vitis by AMD/Xilinx
      - Quartus Prime by Intel/Altera
      - ...

# ASIC P&R

- Complex part of the design flow made of three main steps.
  1. Floorplanning
  2. Placement
  3. Routing

# Floorplanning

- Define chip organization:
  - Pin position
  - Power supply
  - Area for cells
  - Area for routing
  - ...

# Placement

- Know area reserved for cells placement → from flooplanning
- Know layers and cells geometry → lef files

```
/* layers definition */  
LAYER nwell  
    ...  
END nwell  
...
```

```
/* cells geometry definition */  
MACRO nand2  
    CLASS CORE ;  
    ORIGIN 0.000 0.000 ;  
    SIZE 1.380 BY 2.720 ;  
    ...  
    PIN A  
        DIRECTION INPUT ;  
    ...  
    PORT  
        LAYER li1 ;  
        RECT 0.940 1.075 1.275 1.325 ;  
    END  
END A  
...  
END nand2
```

# Note

- In order to accommodate different cells in one row, cells have the same height and different width:
- E.g. (from LEF file)
  - NAND2 → SIZE 1.380 BY 2.720
  - D-FF → SIZE 9.200 BY 2.720

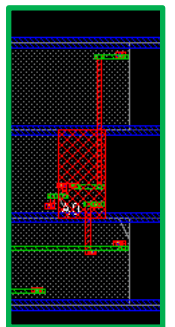
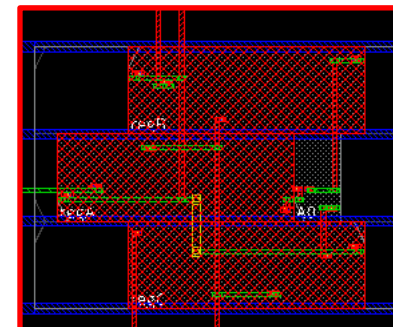
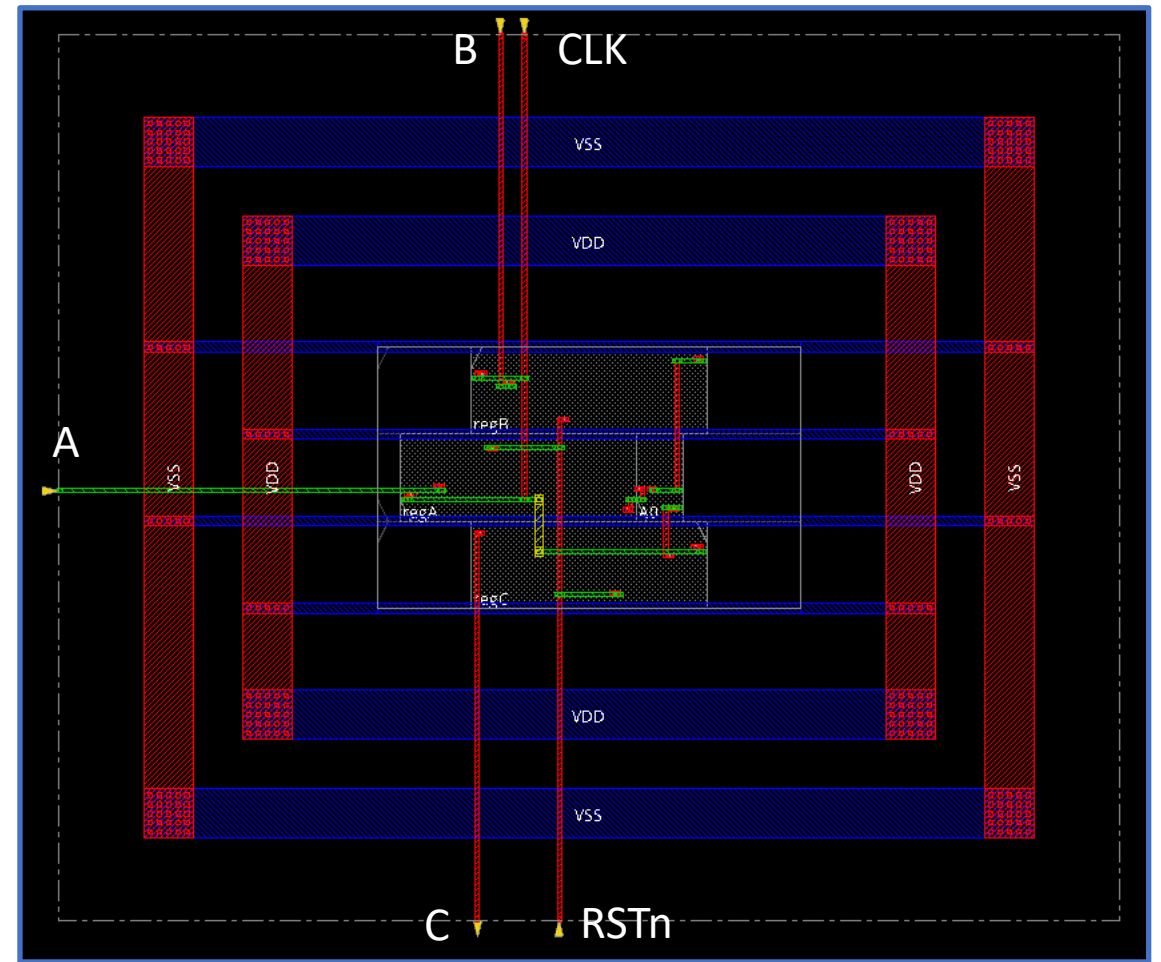
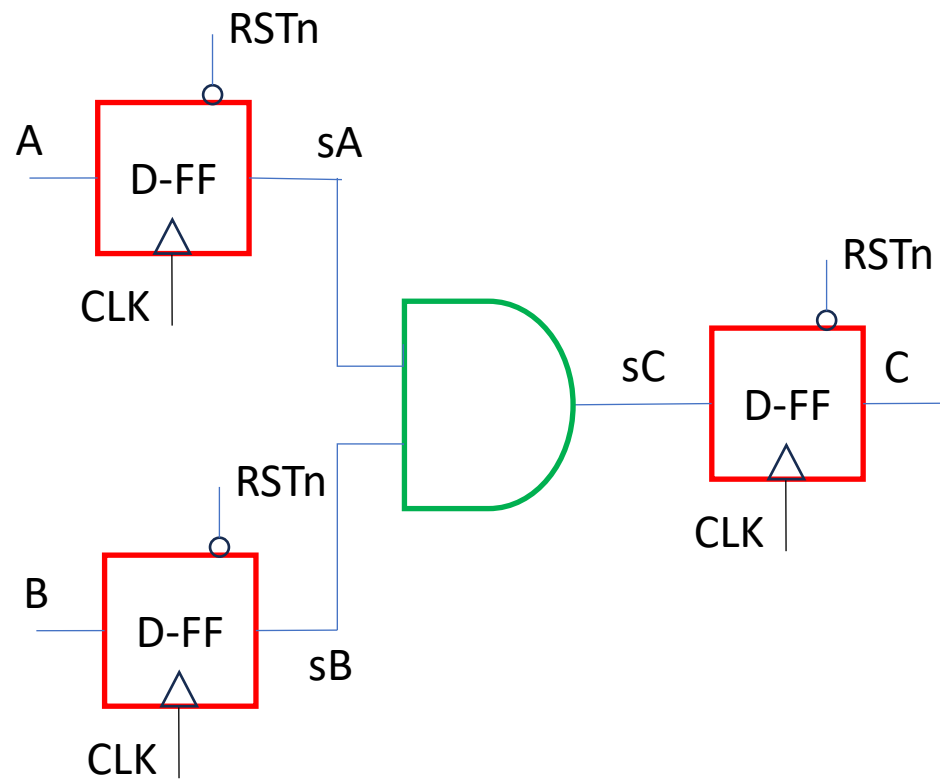
# Routing

- Know area reserved for wires → from flooplanning
- Know metal layers geometry → lef files

```
LAYER met1  
  TYPE ROUTING ;  
  DIRECTION HORIZONTAL ;  
  ...  
END met1
```



# Example



# FPGA P&R

- Simplified version of the ASIC P&R
  - Structure already defined
  - Find where to place logic to minimize routing delay
- Final result is a bitstream which configures the PLD according with the result obtained after P&R.
- The bitstream is loaded on the PLD
  - SRAM based
  - Flash based
  - ...

# Intellectual Properties (IPs)

- Reusable units developed to be used as building blocks in different designs.
- E.g.
  - Microprocessors
  - Memories
  - Accelerators
  - Interfaces/protocols
  - ...

# Advantages and challenges

- Fast time-to-market, reduced cost
- Verification and compatibility
- Security and licensing